

# Development and Applications of "Mössbauer Cameras"

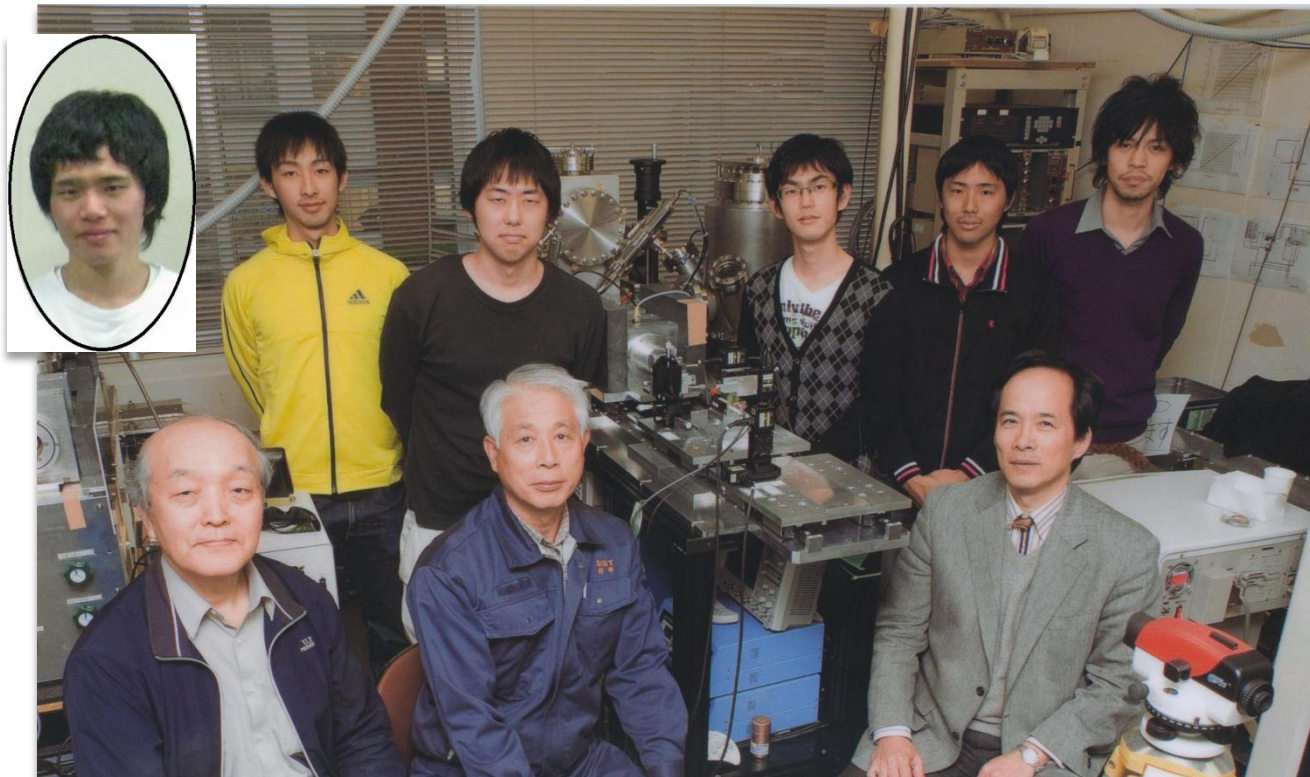
Y. Yoshida

Shizuoka Institute of Science and Technology, Japan

1. Introduction
2. "Mössbauer Camera" : **imaging** by PIAS+FOS
3. "Mössbauer Camera" : **mapping** by MCX
4. **Applications** for Fe impurity in Si-solar cells
5. A running project to achieve **submicron resolution**\*
6. Summary

\* Supported by JST

# Mössbauer Group at SIST



Kazuo Hayakawa<sup>1</sup>, Kenichi Yukihiro<sup>1</sup>, Masahiro Ichino<sup>1</sup>,  
Yuki Akiyama<sup>1</sup>, Hiroto Kumabe<sup>1</sup>, Hiroyoshi Soejima<sup>2</sup>

<sup>1</sup> Shizuoka Institute of Science and Technology, <sup>2</sup> Shimadzu Corporation

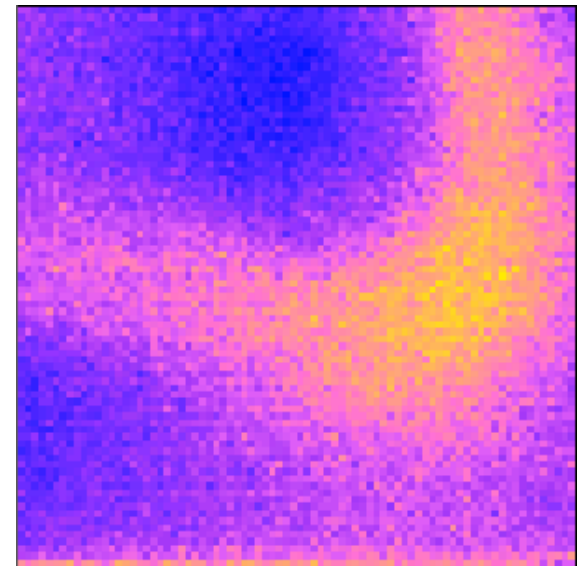
# "Mössbauer camera" to study microstructures in materials

CCD camera



800×800 pixels

Mössbauer camera



↔  
1mm

80×80 pixels

Readout time is too slow in  
X-ray camera (30ms)

# "Mössbauer Camera" using PIAS + FOS

5cmx5cm / 500x500 pixels

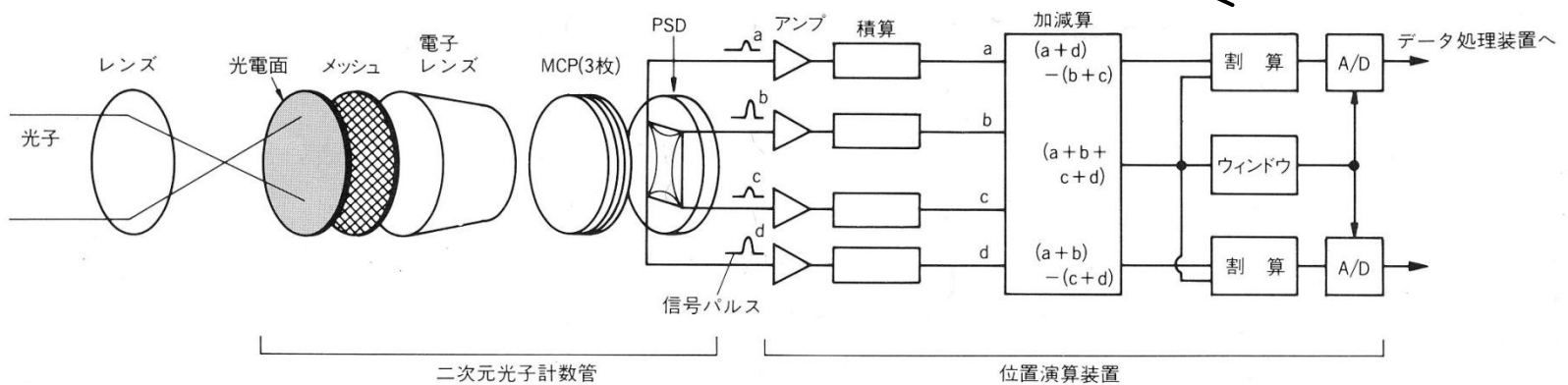
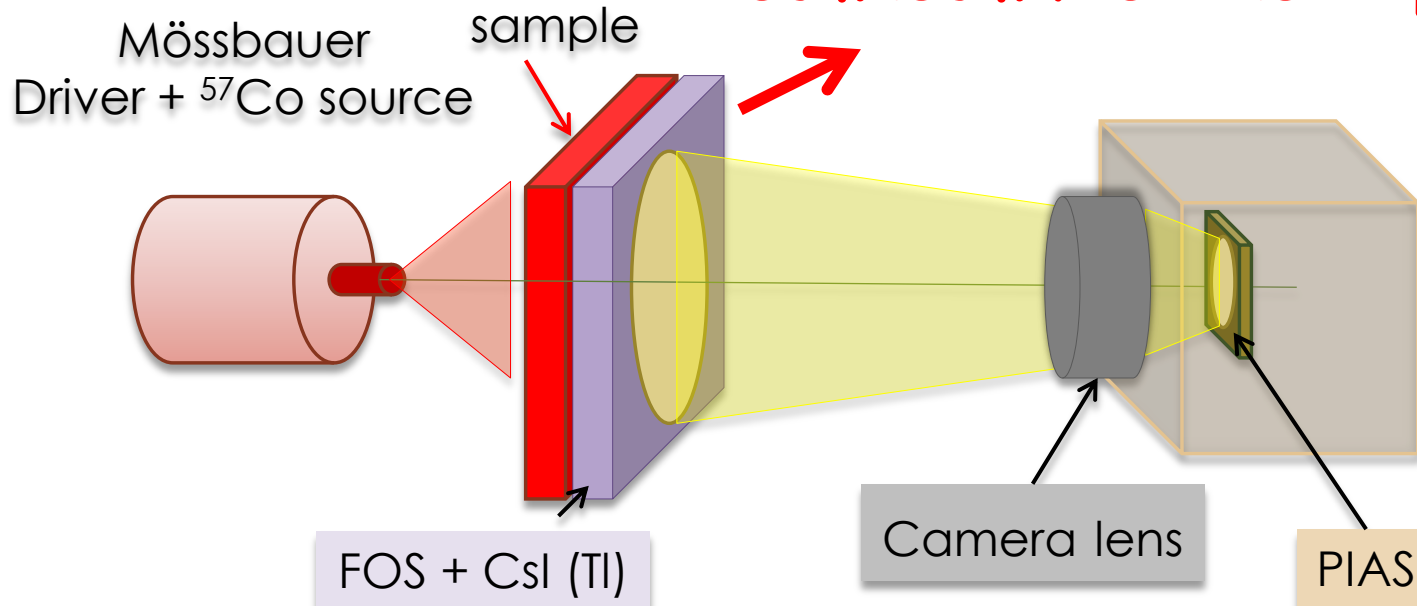
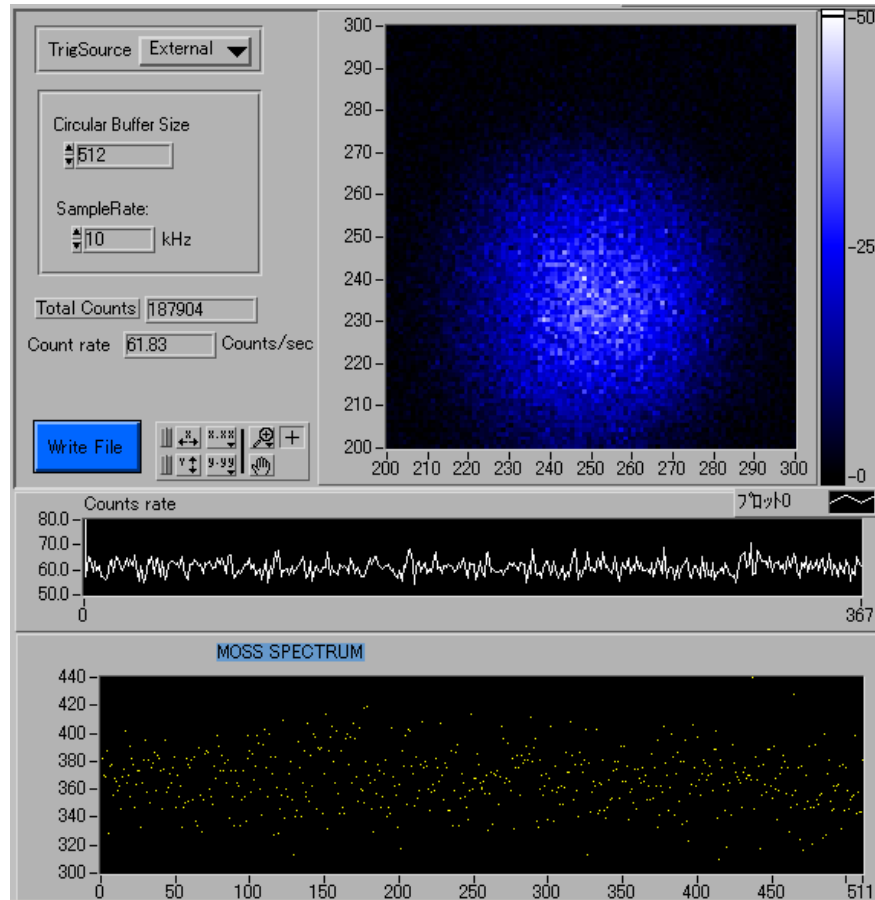


図7. PIAS-TIの動作原理図

# Imaging by PIAS + FOS



# "Mössbauer Camera" using a mapping Technique

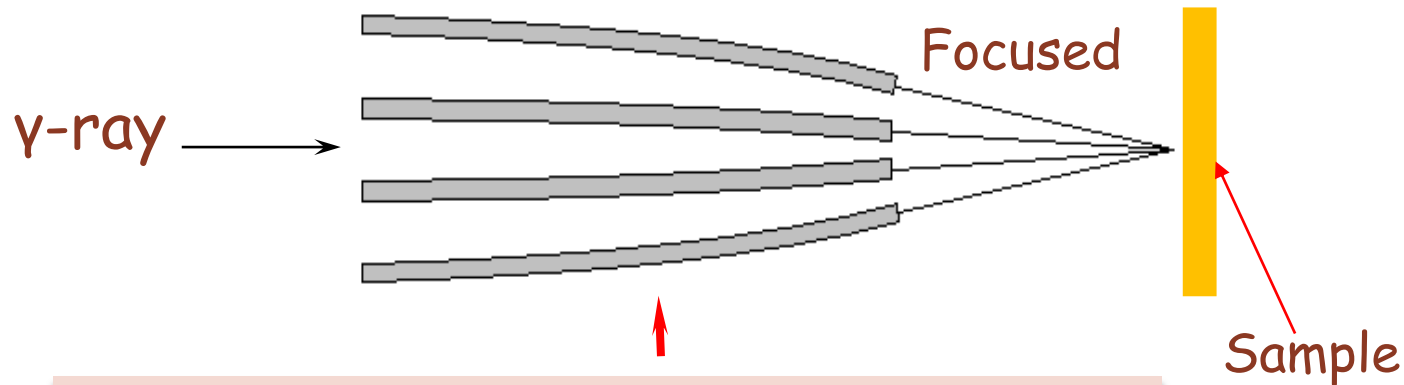
Main program with LabVIEW



# Mössbauer camera: mapping by focusing 14.4keV $\gamma$ -ray

SIST Y. Yoshida, K. Hayakawa, K. Yukihiro, K. Suzuki, K. Sakata, T. Kamimura  
Shimazu H. Soejima

14.4keV  $\gamma$ -ray emitted from a  $^{57}\text{Co}$ -in-Rh source (50mCi)  
are focused on a sample by **MCX lens (Soejima-Kumakov lens)**

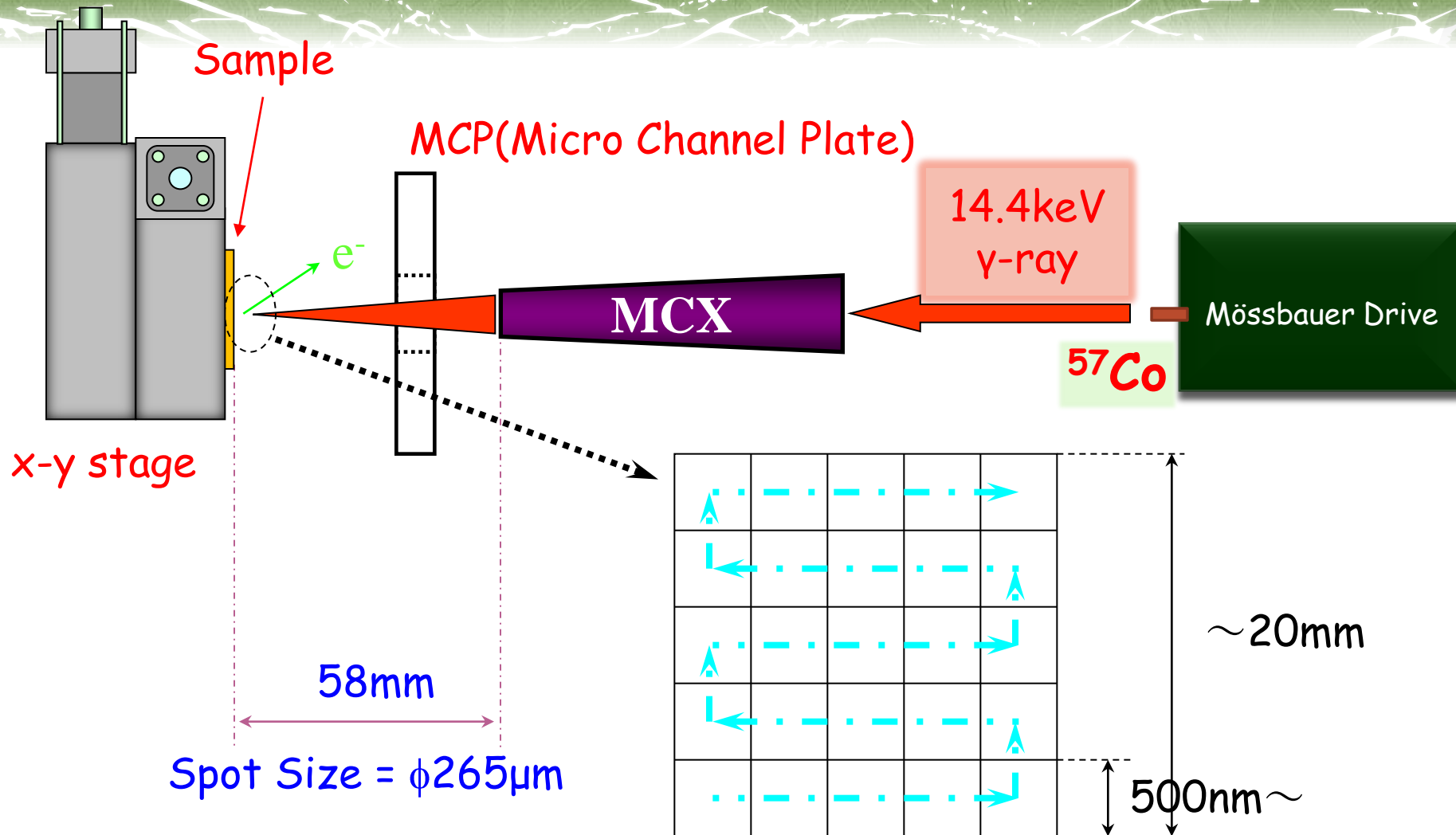


Total reflections of  $\gamma$ -ray in the capillaries

- focal distance : 58mm
- entrance diameter: 4mm $\phi$
- spot size : 265 $\mu\text{m}\phi$
- transmission : 41% for 14.4keV

H. Soejima, Japan Patent 2014379(1986); 2001797(1988)

# A mapping technique for Mössbauer spectroscopy

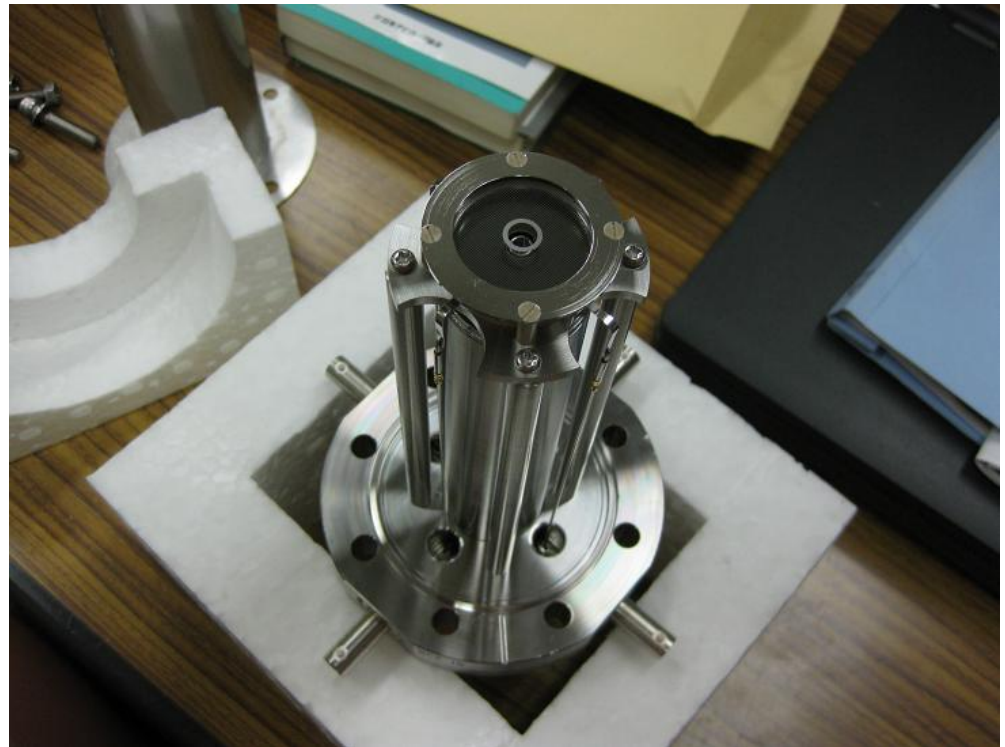
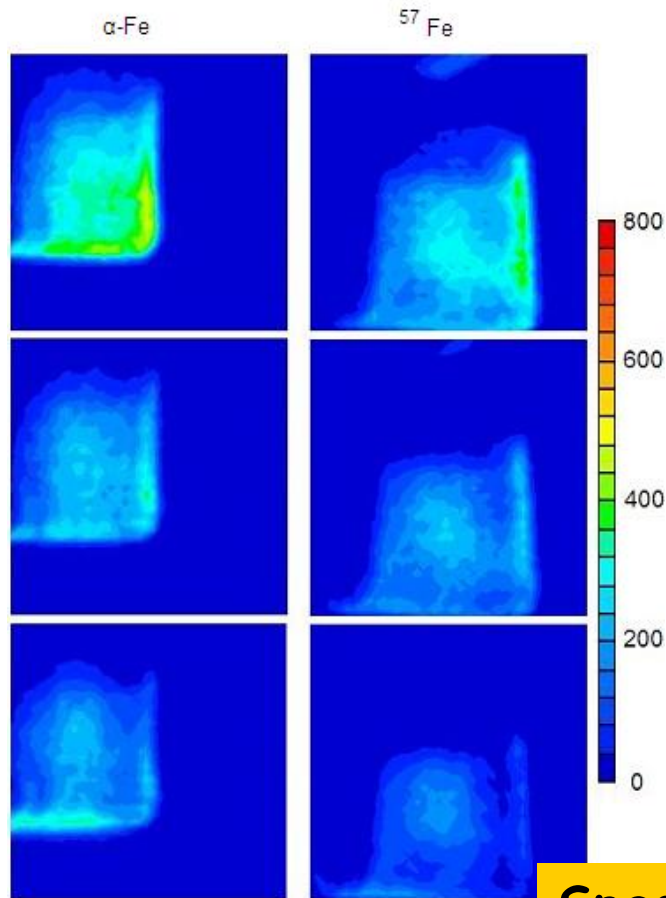


A measurement position is varied with a step size between  $250\mu\text{m}$  and  $25\mu\text{m}$



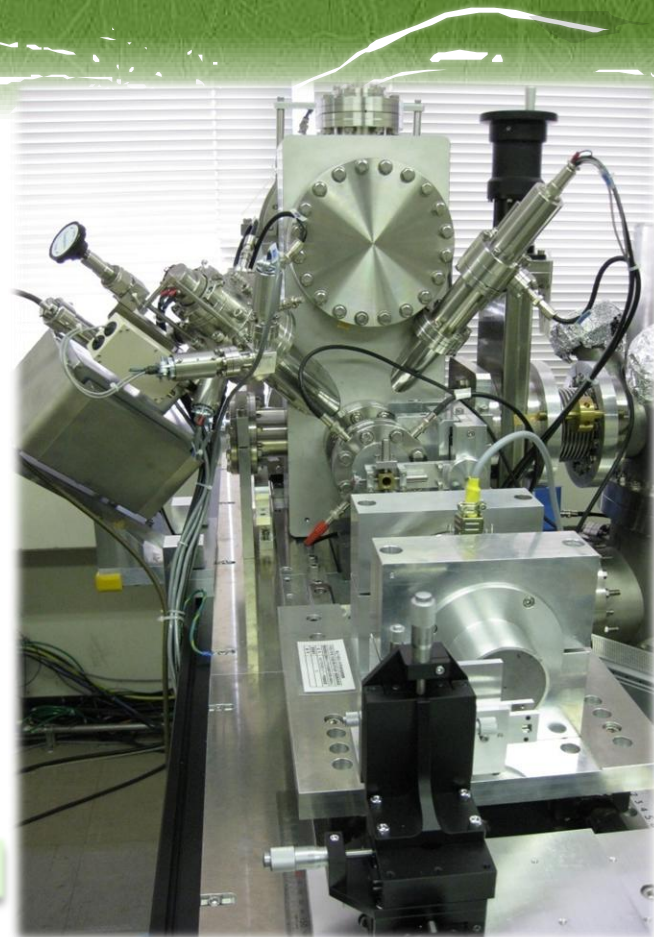
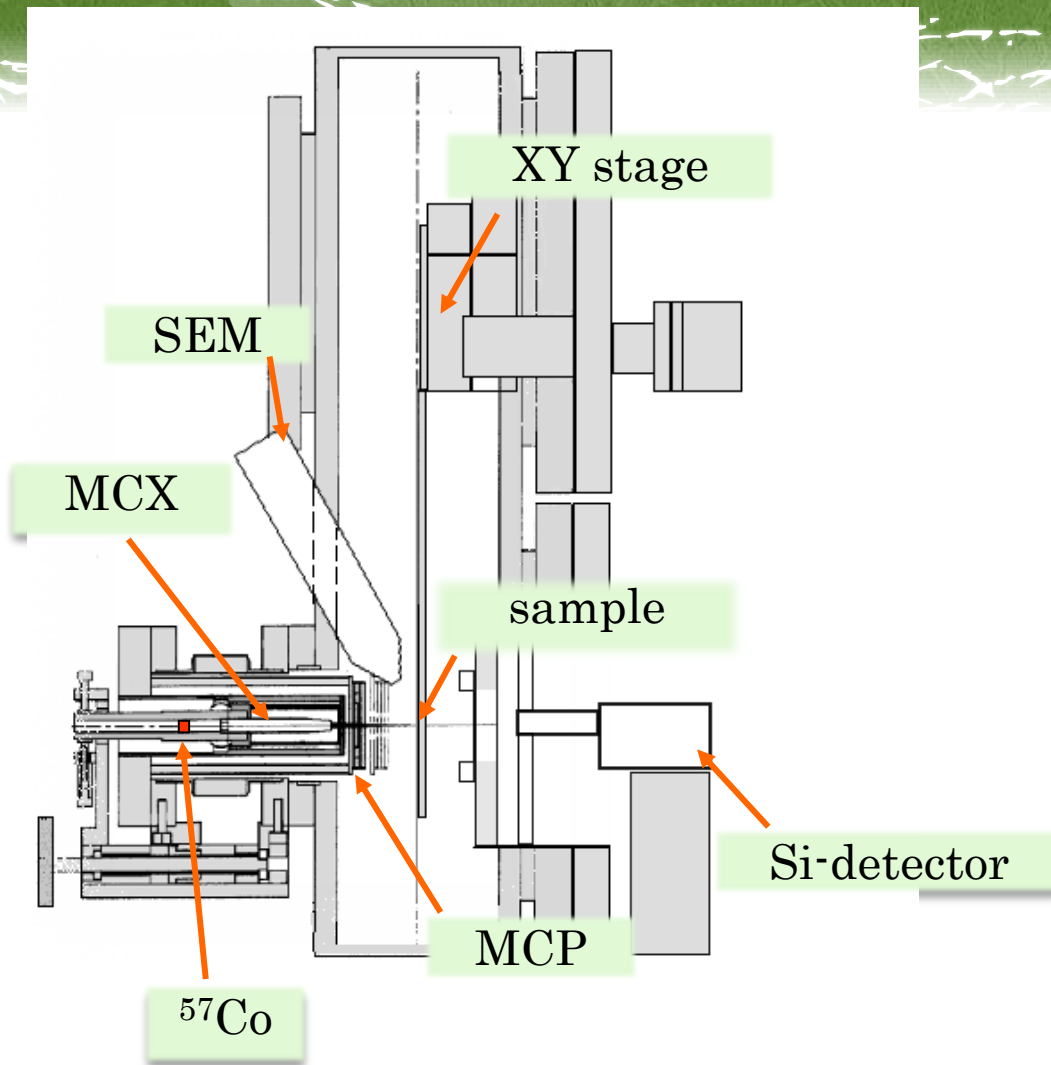
# Three stage MCP with a center hole and a grid

Hamamatsu Photonics K.K.



Space resolution : 50~ 100 $\mu\text{m}$   
The images are distorted at boundaries!

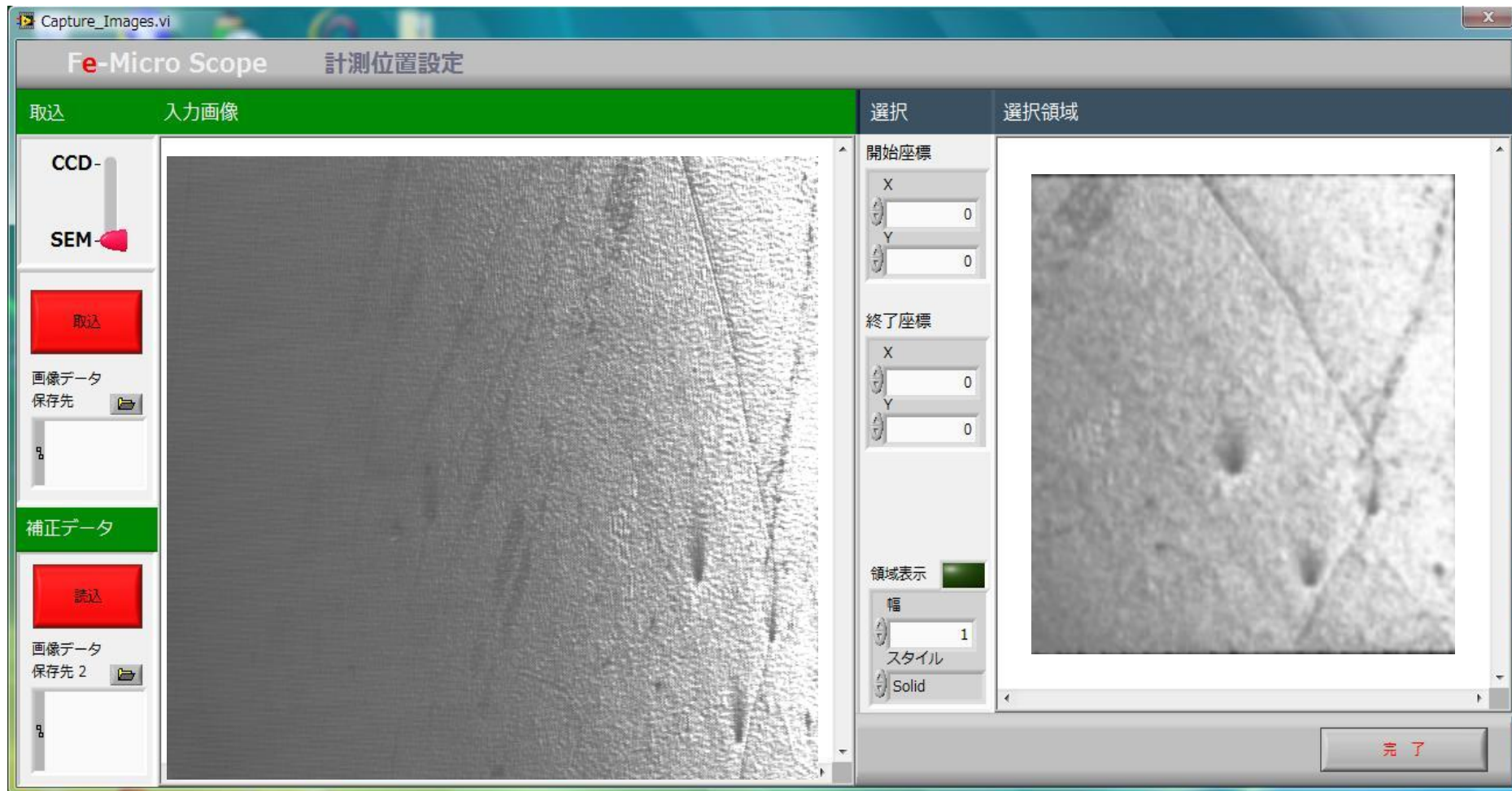
# Instrumental set-up



Vac  $\sim 10^{-5}$  Pa

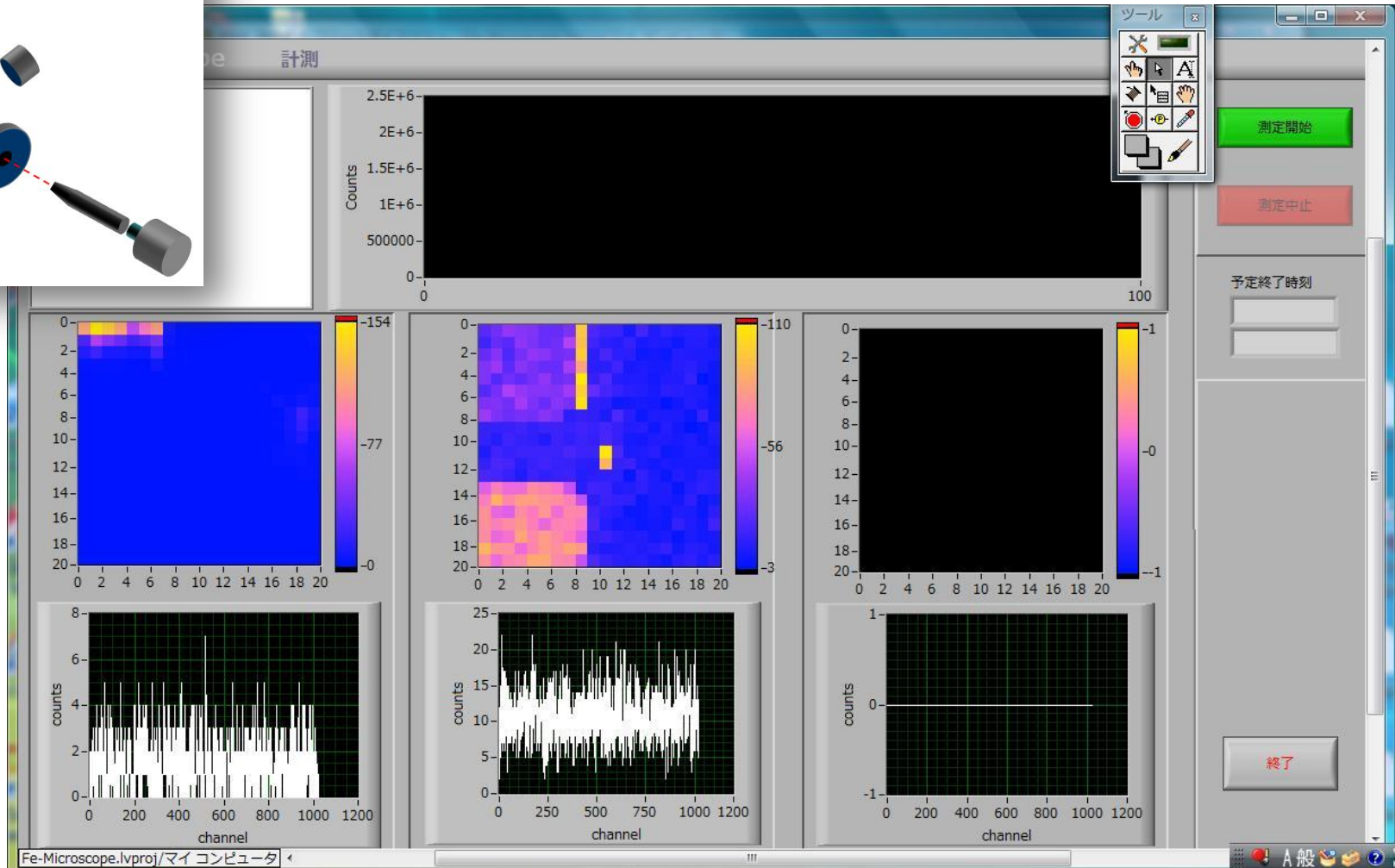
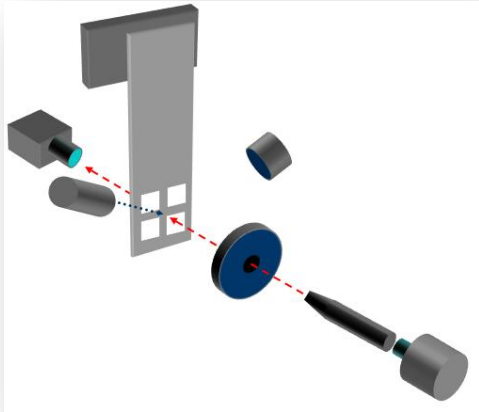
# Mössbauer Camera using a mapping Technique

How to select an observation area by FE-SEM?

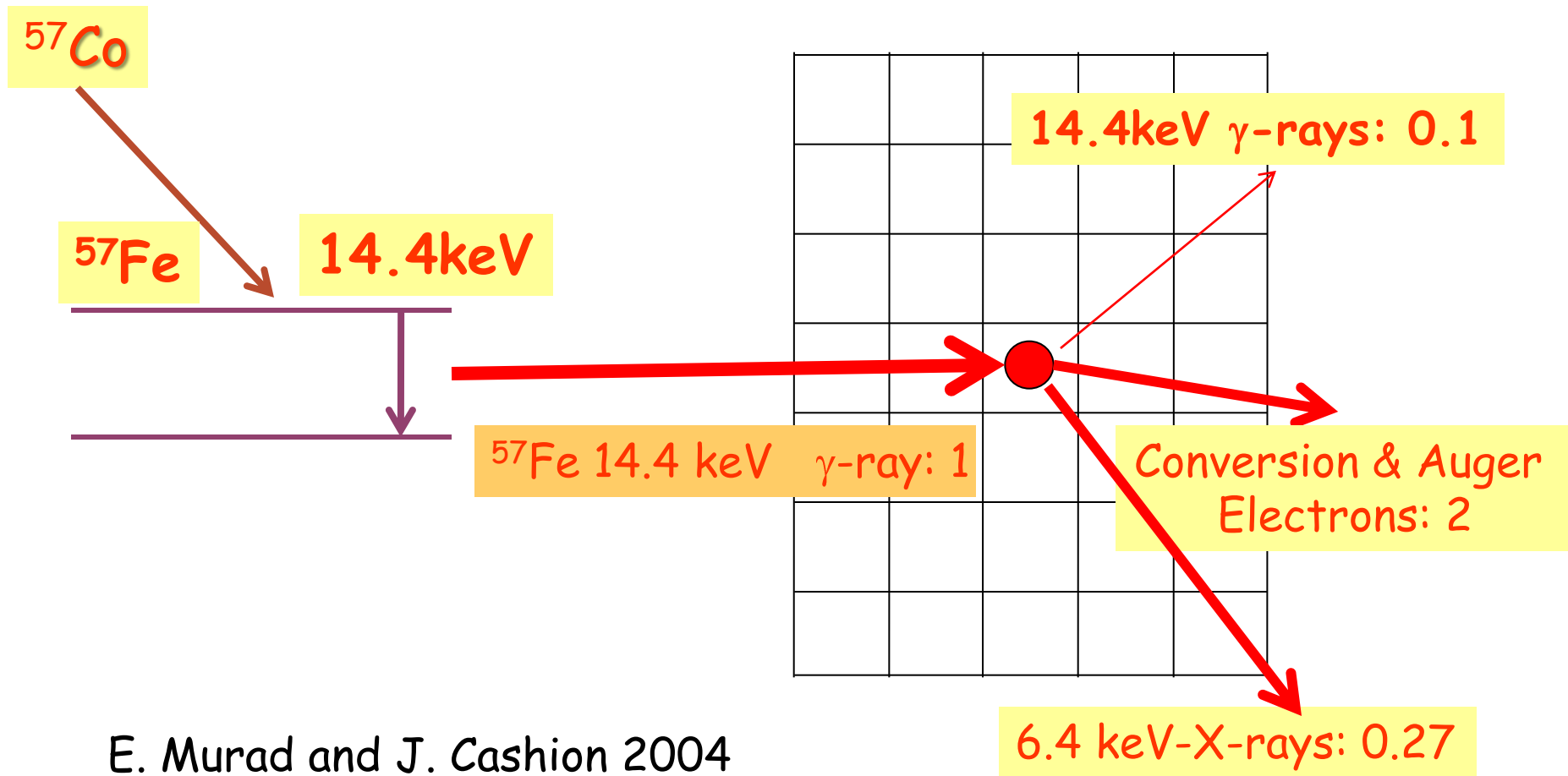


# Mössbauer Camera

How to proceed the microscope operation corresponding three different input?



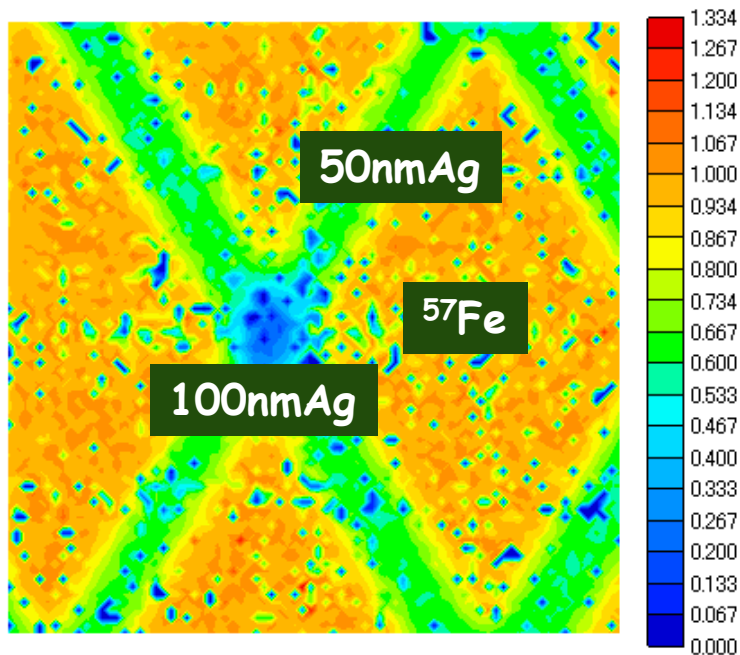
# $^{57}\text{Fe}$ Mössbauer Effect



E. Murad and J. Cashion 2004

# Image Simulations for $100\text{nm}^{57}\text{Fe}+50/100\text{nm-Ag}$ in the case of conversion and Auger electrons mapping

emission ( Counts= $1\pm 1$ )



emission ( Counts= $10\pm 3$ )

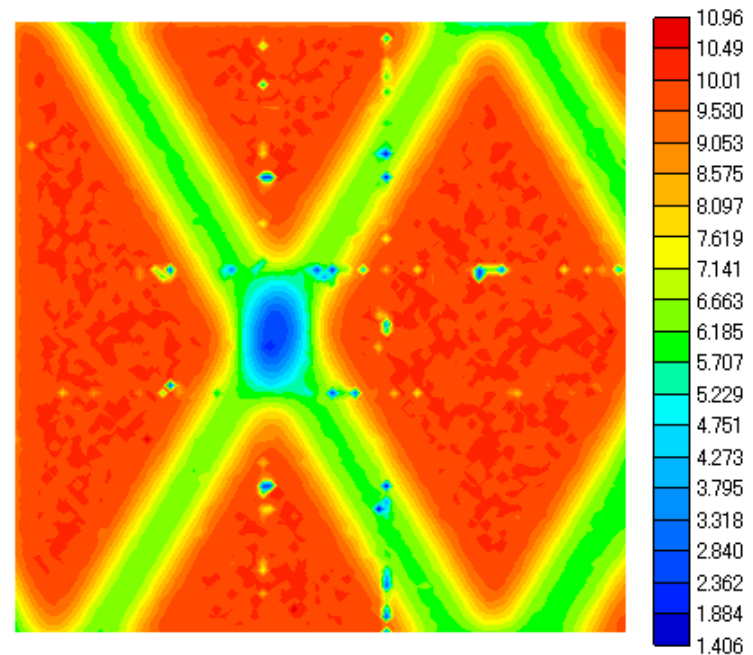
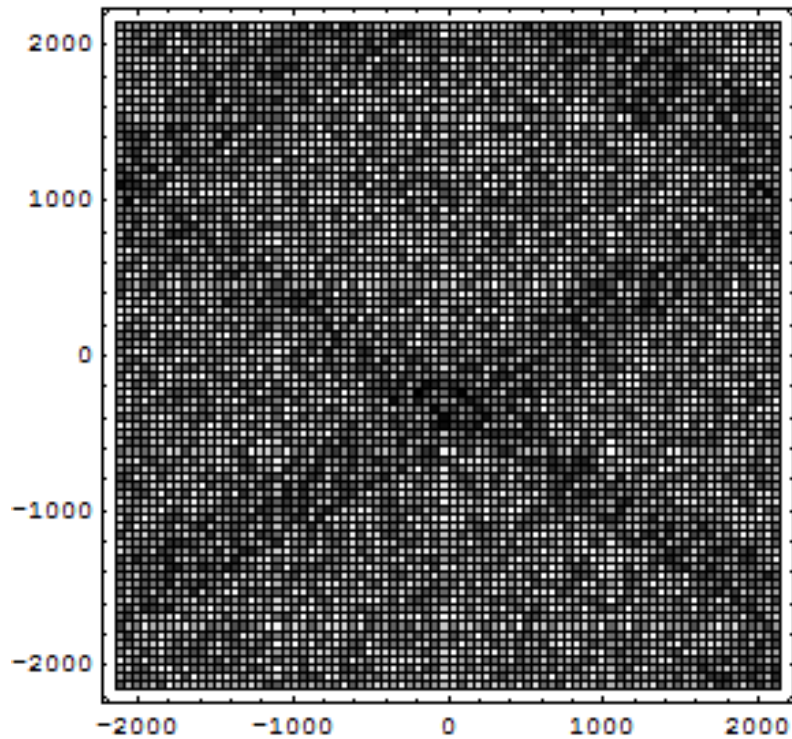
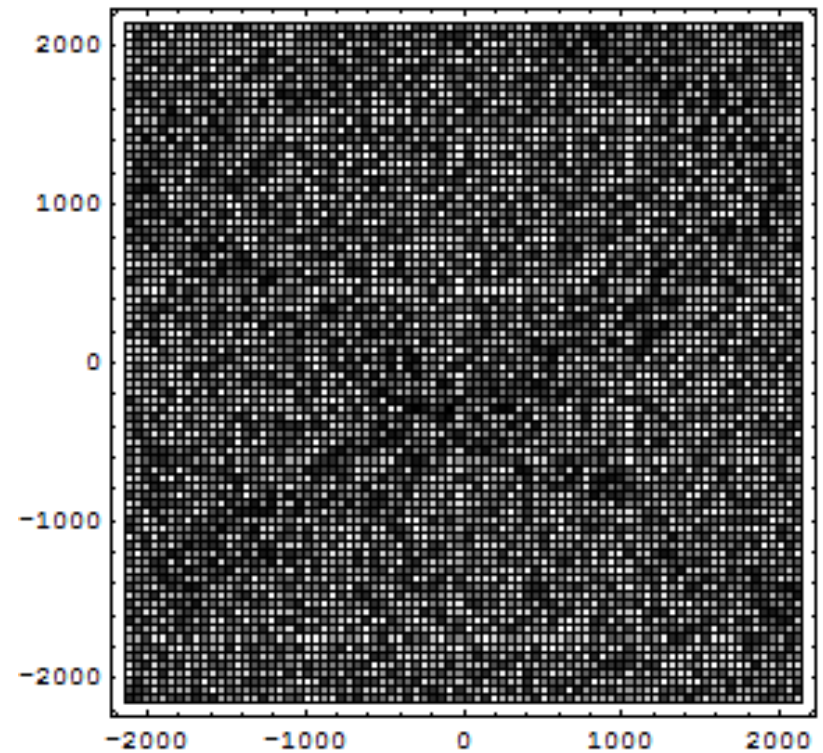


Image Simulations for  $100\text{nm}^{57}\text{Fe}+50/100\text{nm}-\text{Ag}$   
in the case of transmitted  $14.4\text{keV}-\gamma$ -rays mapping

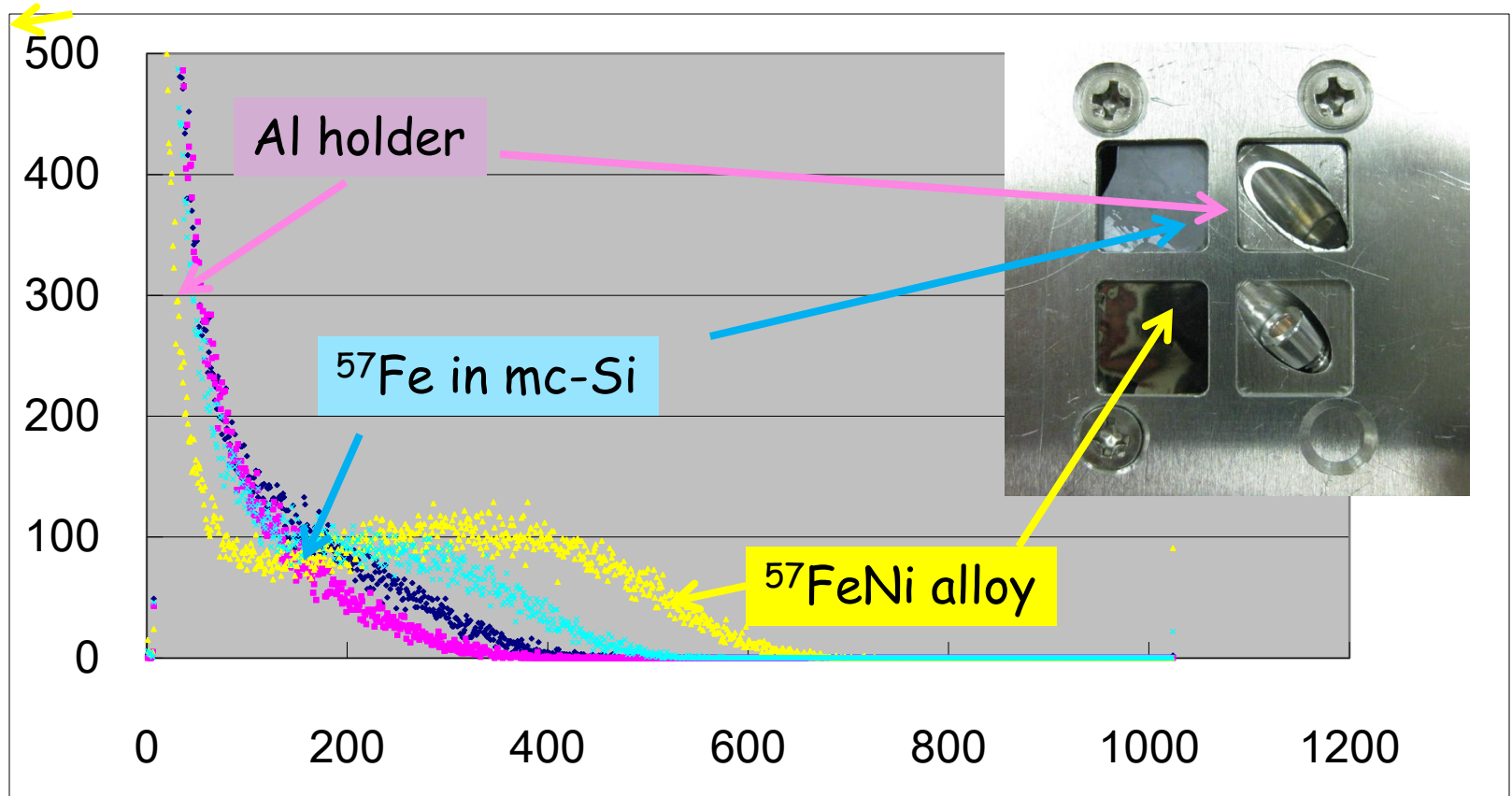
transmission  
( Counts= $50000\pm 224$ )



transmission  
( Counts= $10000\pm 100$ )



# PHA spectra from MCP which depend on the energy of electrons ?



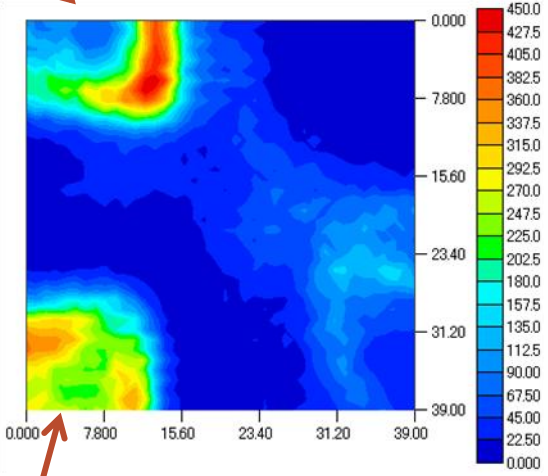
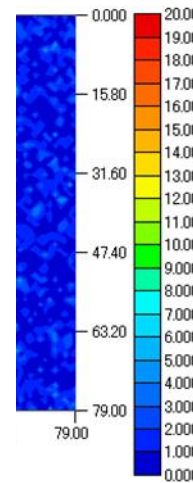
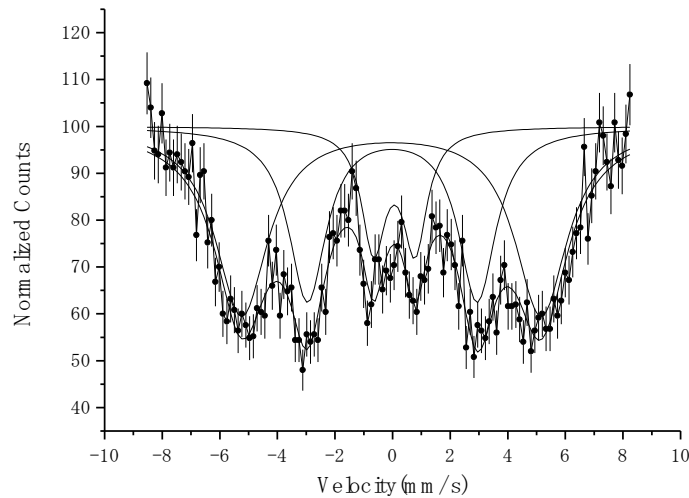


# Simultaneous measurements of mapping images using transmission and emission geometry

$^{57}\text{Fe}$  deposited mc-Si

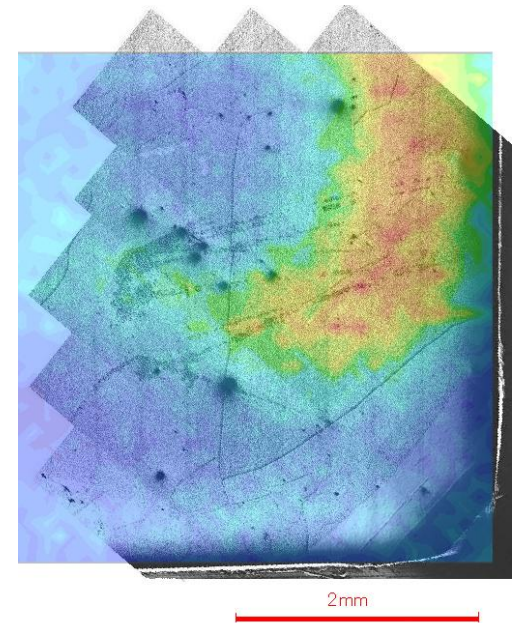
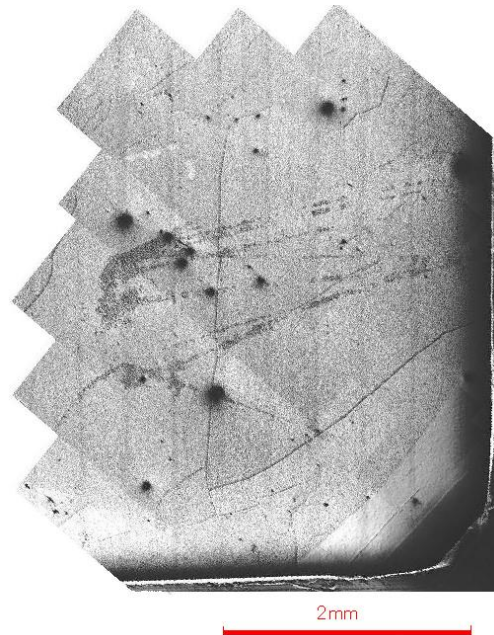
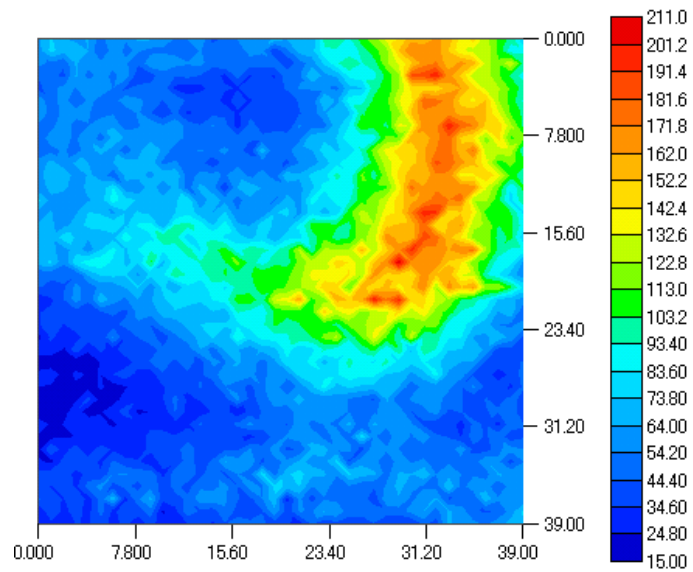
14.4keV- $\gamma$ -rays

electrons

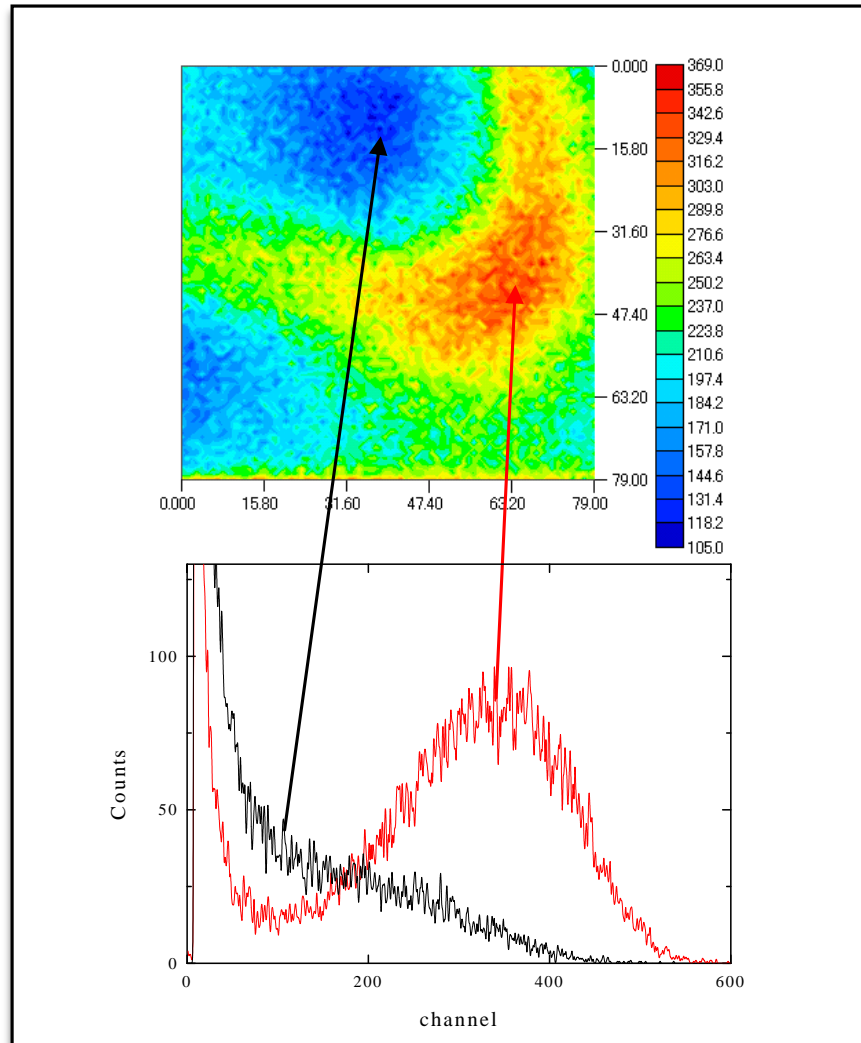


$^{57}\text{Fe}$  enriched FeNi alloy

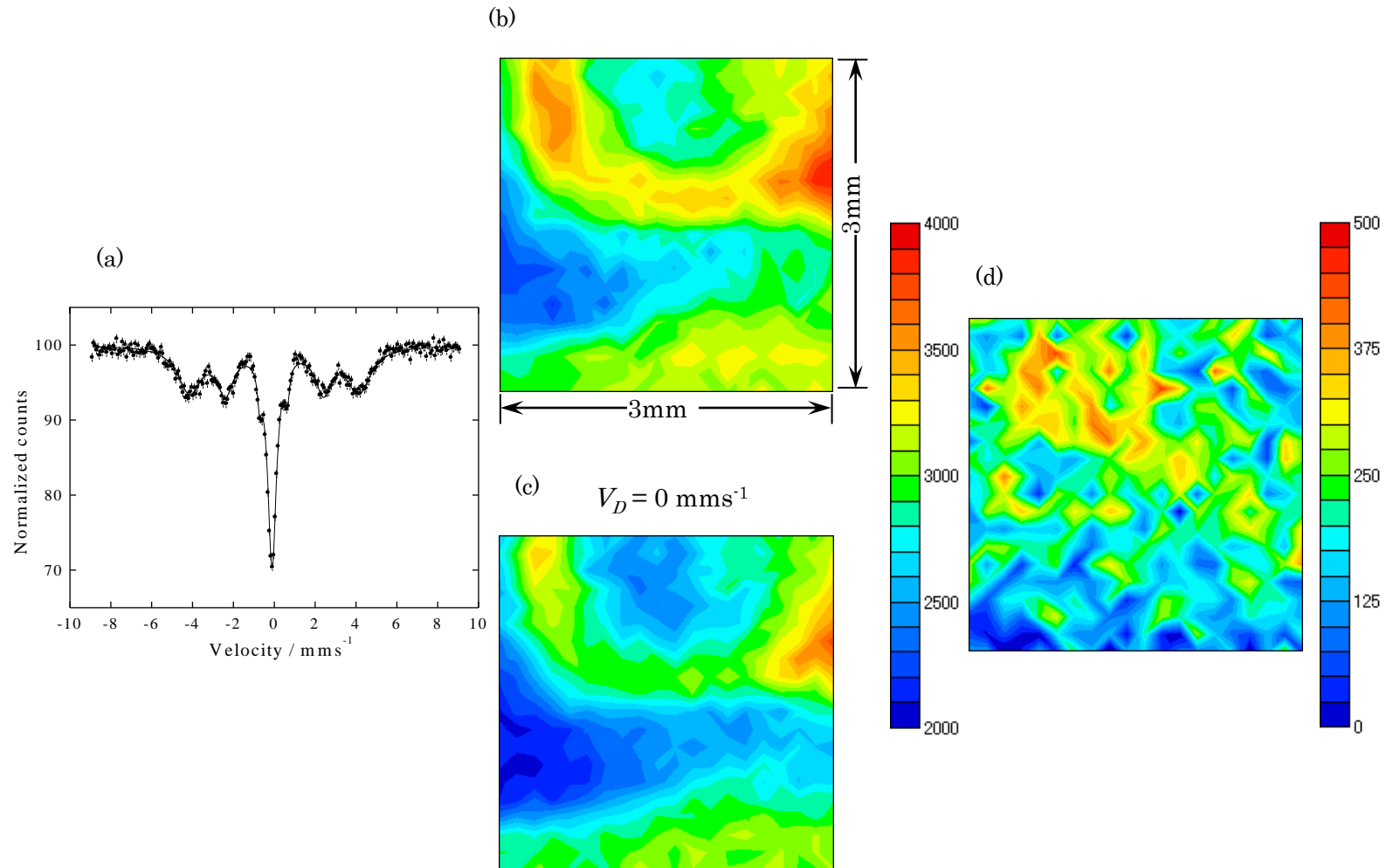
# A mapping image of electrons and FE-SEM picture



# PHA spectrum of MCP corresponding to the measuring points



# Mapping picture of SUS304

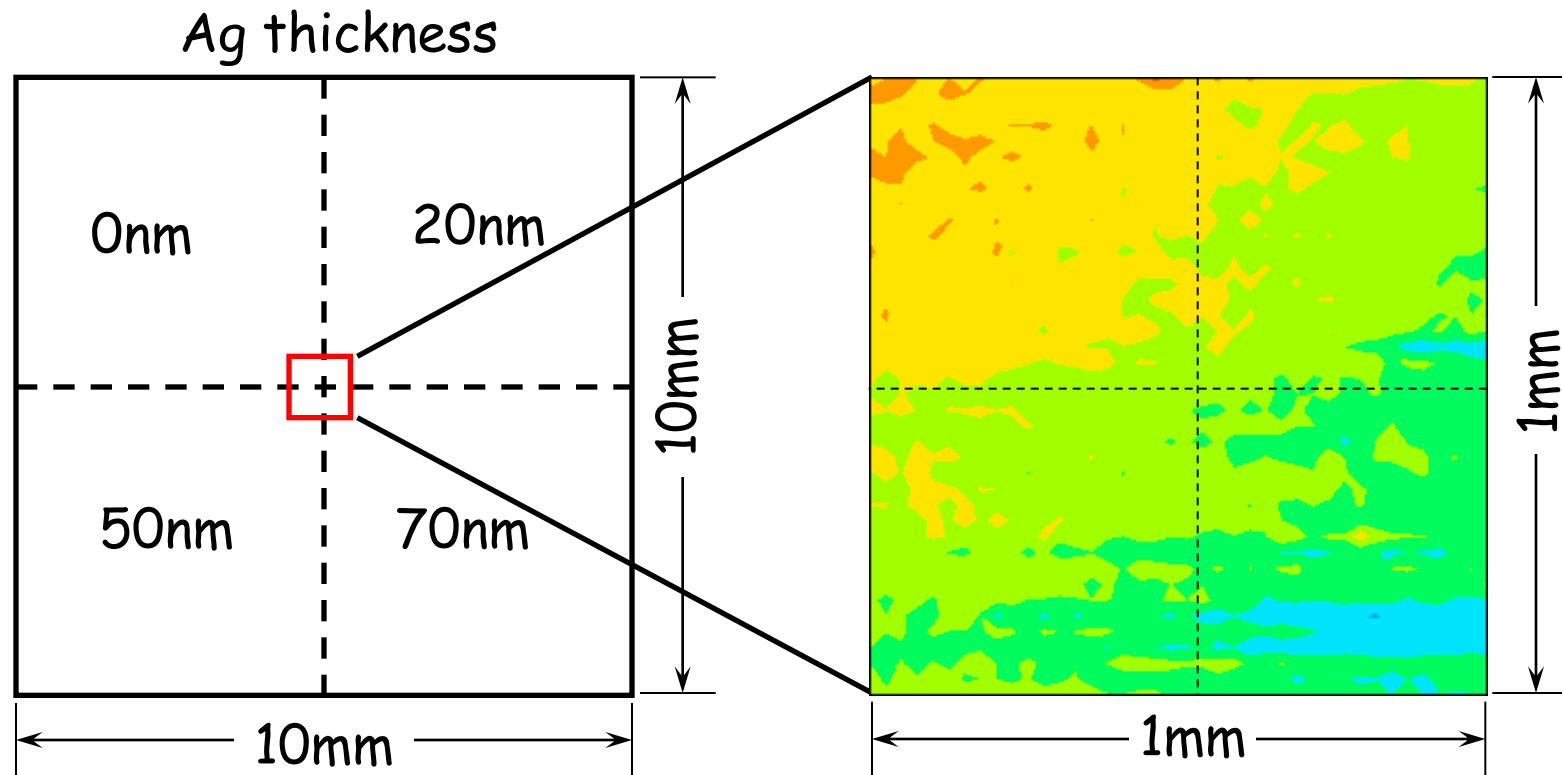
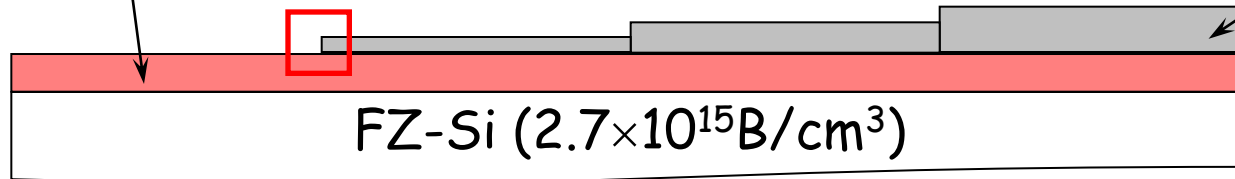


# Observed image of $^{57}\text{Fe}$ + Ag deposited FZ-Si

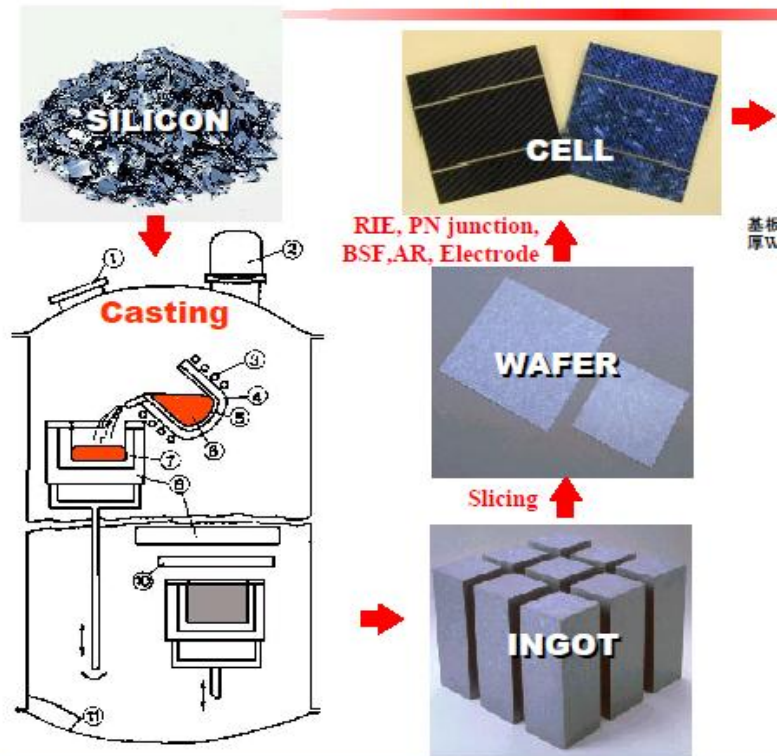
3D mapping may be possible !

$^{57}\text{Fe}$  thickness : 50nm

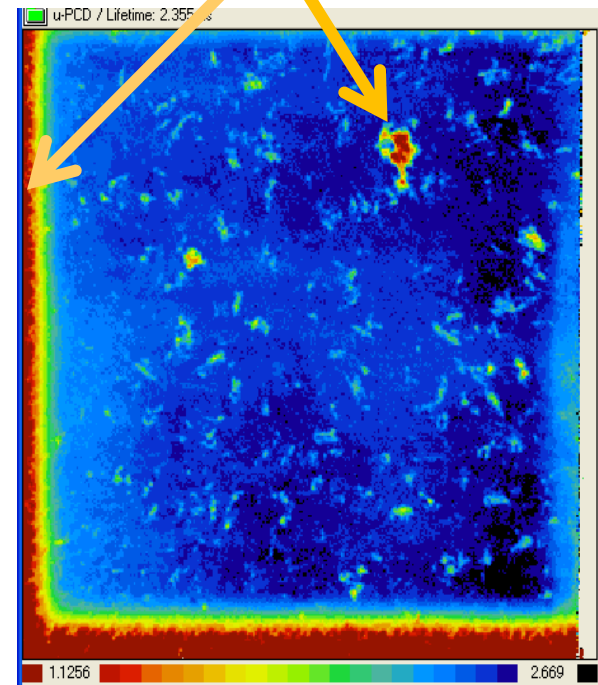
Ag thickness : 20nm~210nm



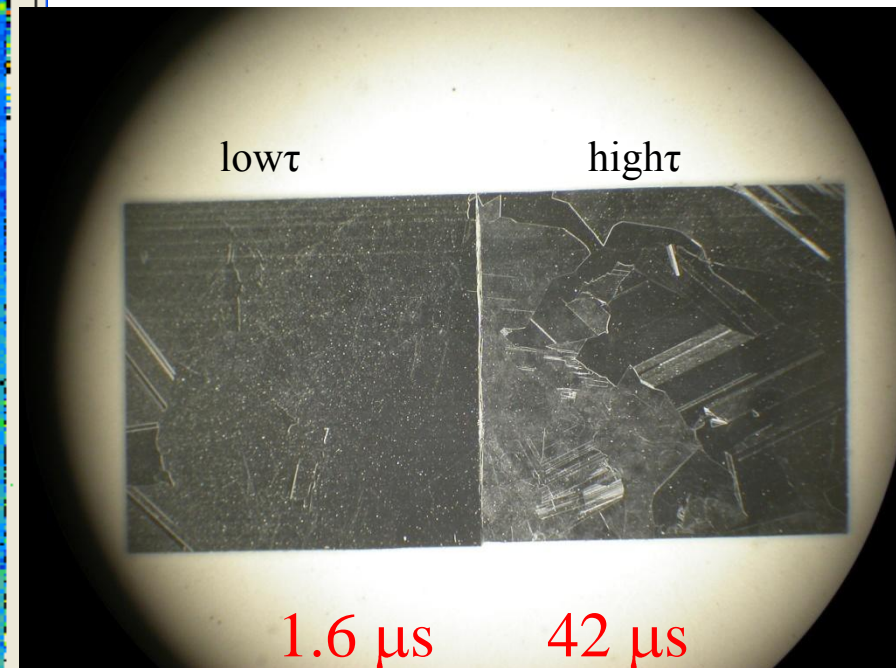
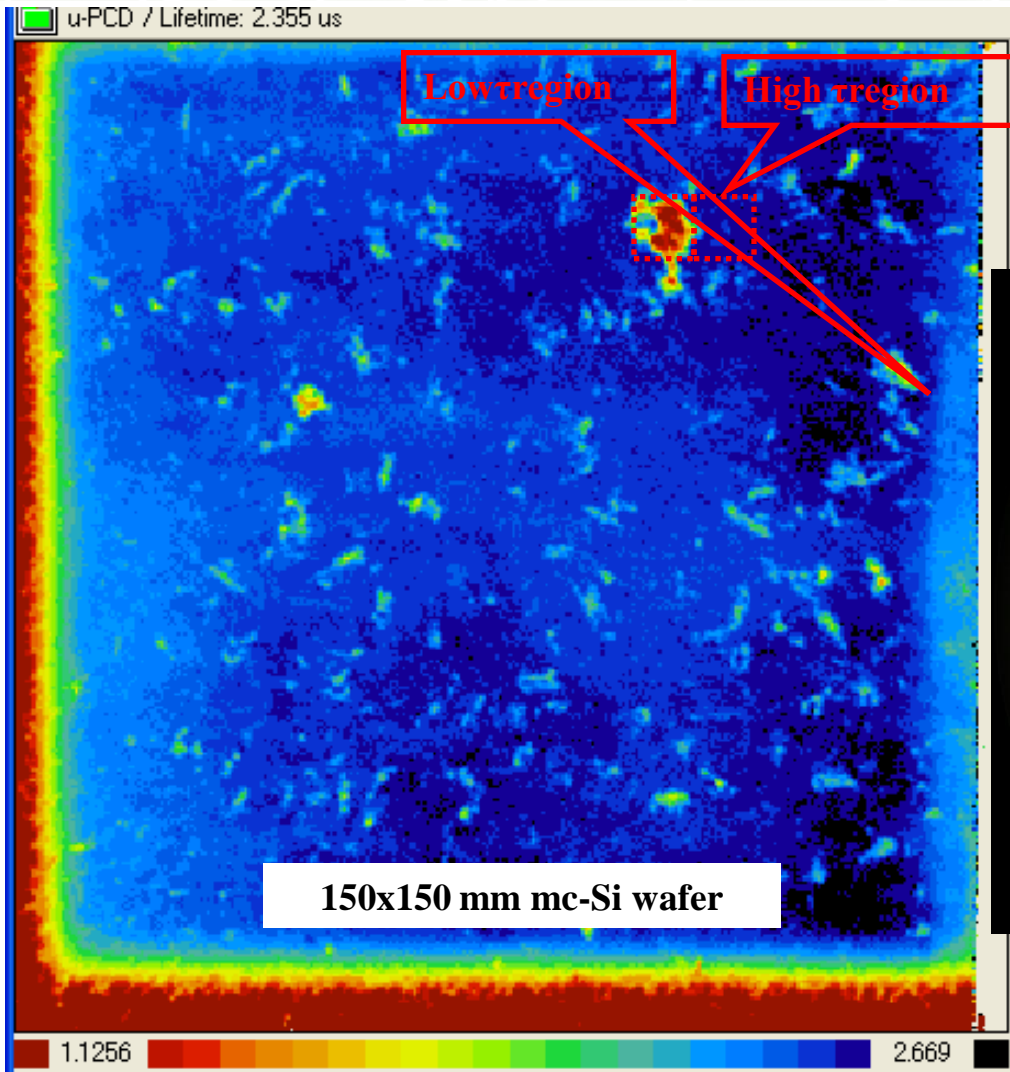
# Application for Fe contamination in mc-Si solar cell



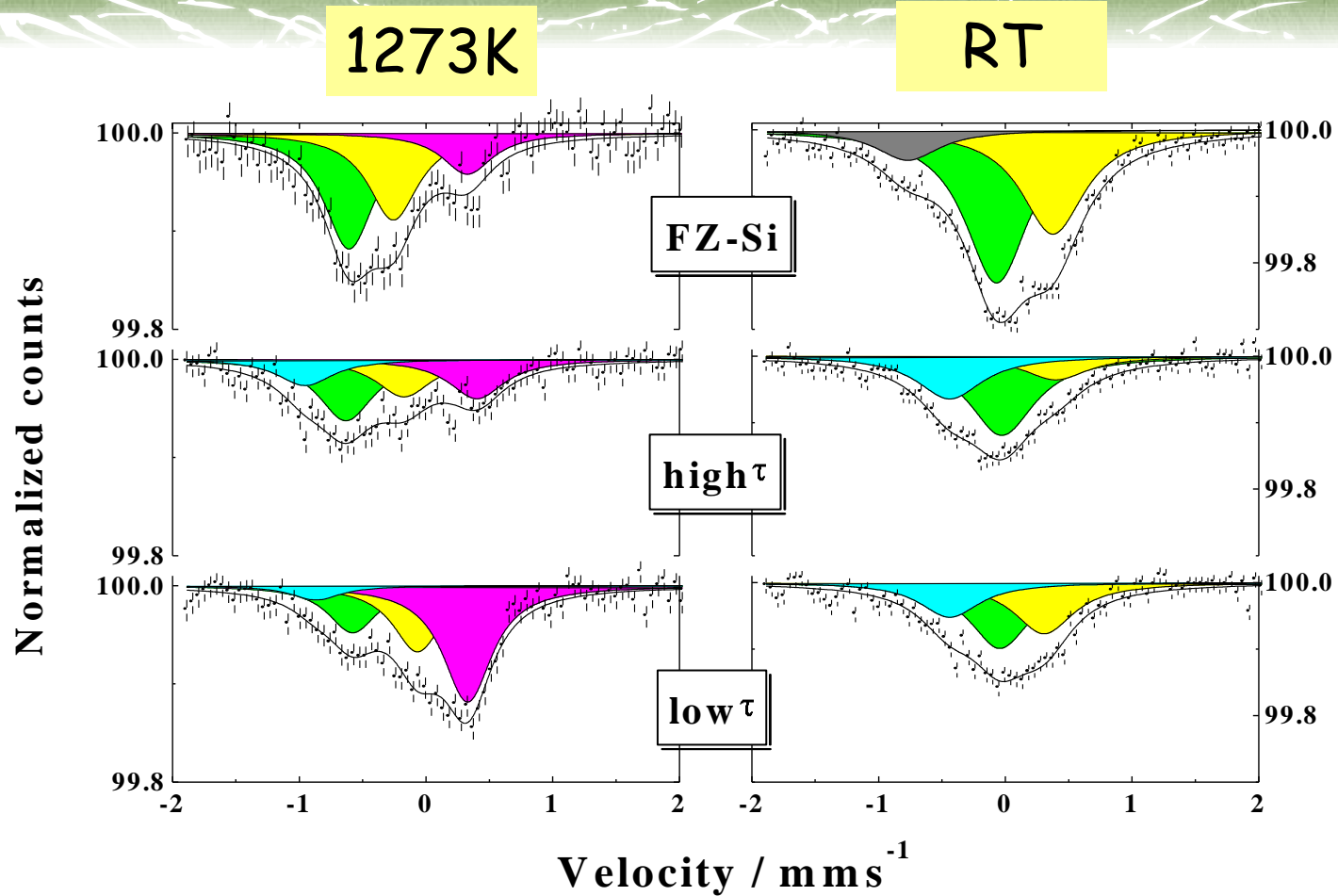
Low efficiency due to defects



# mc-Si wafer contains a region with low minority carrier life time



# Mössbauer spectra of $^{57}\text{Fe}$ doped FZ-Si, mc-Si

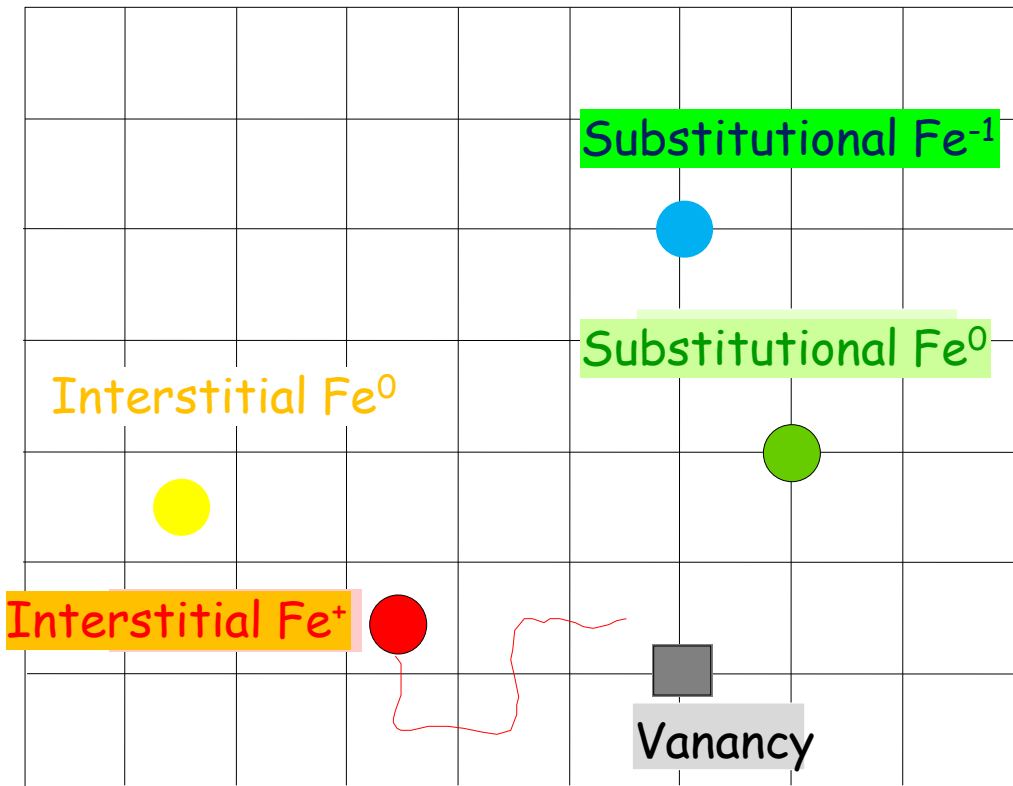


Y. Yoshida, S. Horie, K. Niira, K. Fukui and K. Shirasawa, *Physica B*, 376-377 (2006) 227.

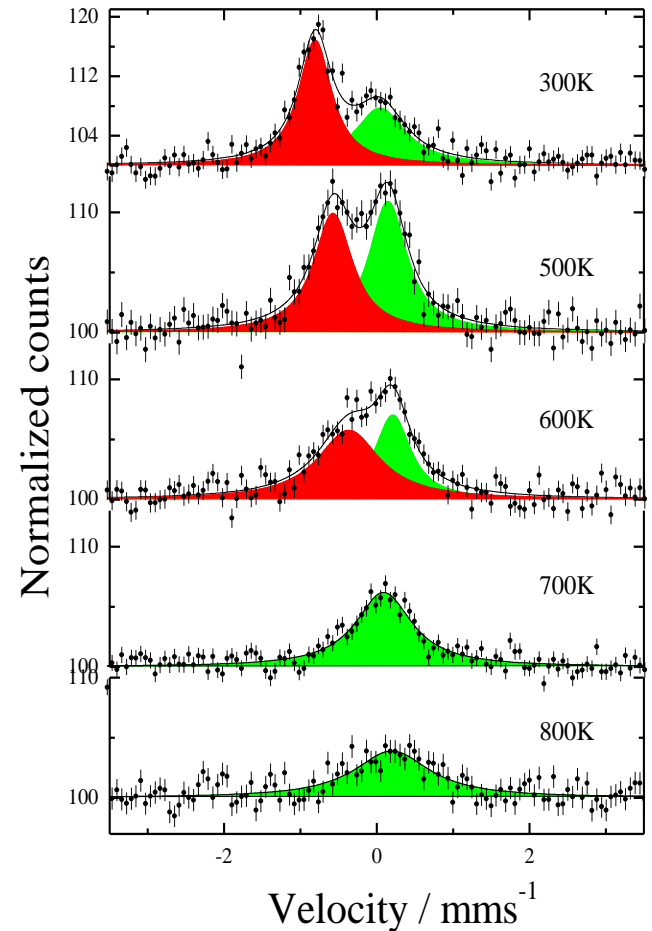


# Atomistic information on $^{57}\text{Fe}$ through Hyperfine interactions between $^{57}\text{Fe}$ nucleus and electrons

## Fe impurities in mc-Si solar cells



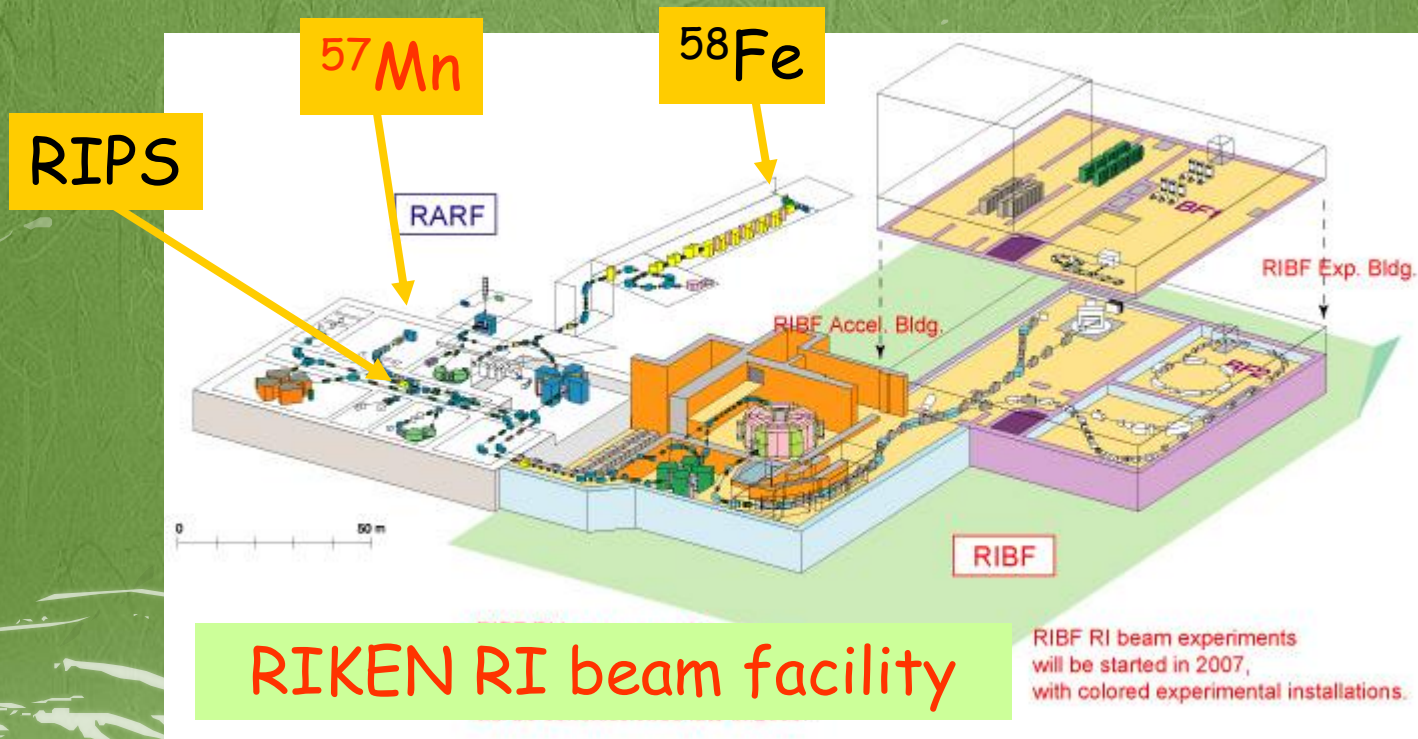
## $^{57}\text{Mn}/^{57}\text{Fe}$ in Si



# FINAL LATTICE SITES AND CHARGE STATES OF $^{57}\text{Mn}$ / $^{57}\text{Fe}$ GeV- IMPLANTATION INTO Si

Y. Yoshida<sup>1</sup>, Y. Kobayashi<sup>2</sup>, K. Yukihiro<sup>1</sup>, K. Hayakawa<sup>1</sup>, K. Suzuki<sup>1</sup>, A. Yoshida<sup>2</sup>,  
H. Ueno<sup>2</sup>, A. Yoshimi<sup>2</sup>, K. Shimada<sup>2</sup>, D. Nagae<sup>2</sup>, K. Asahi<sup>3</sup> and G. Langouche<sup>4</sup>.

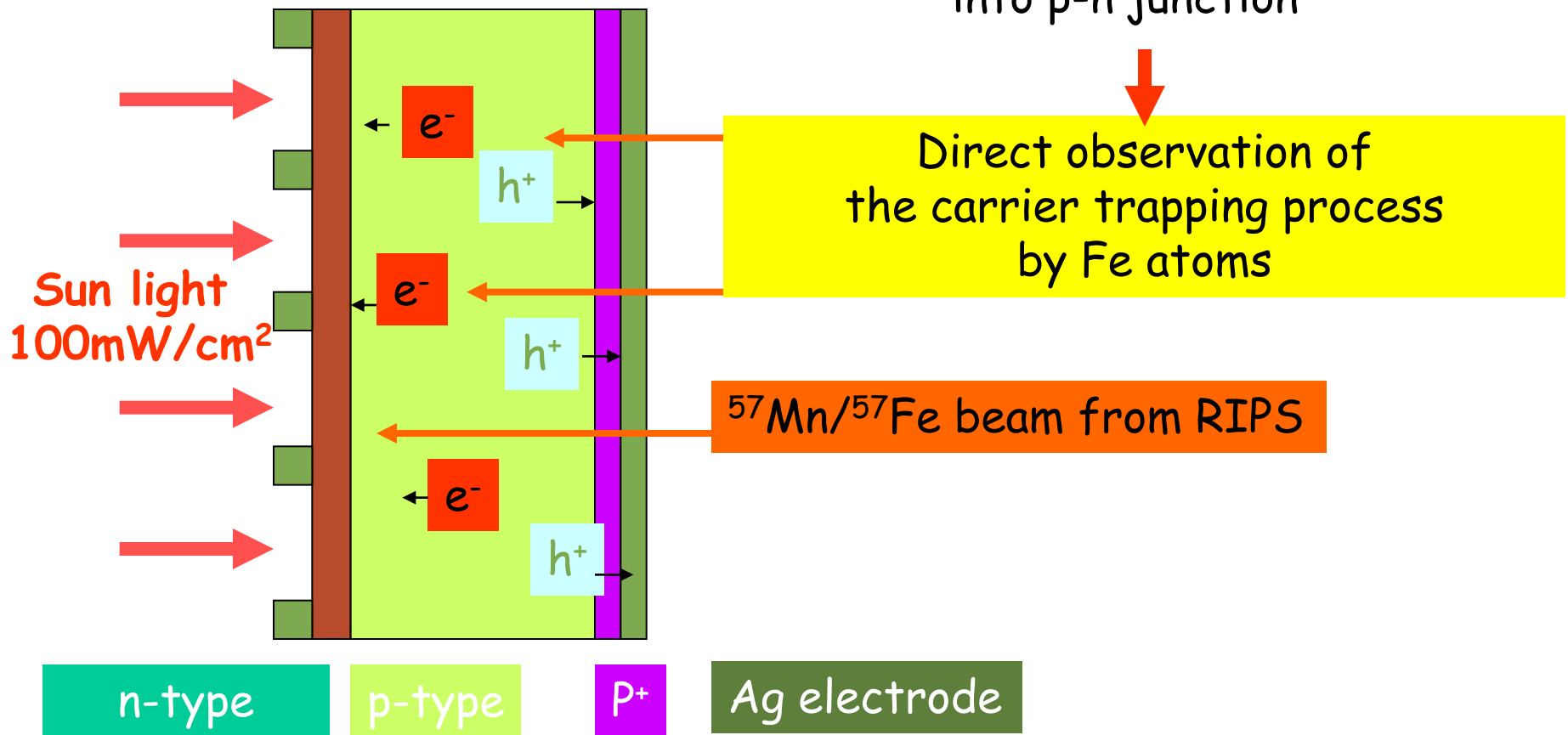
<sup>1</sup> Shizuoka Institute of Science and Technology, Shizuoka, Japan, <sup>2</sup> RIKEN, Japan,  
<sup>3</sup> Tokyo Institute of Technology, Japan, <sup>4</sup> Katholieke Universiteit Leuven, Belgium



# Direct Observation of Fe states in the p-n junction of solar cells during operation under light illumination

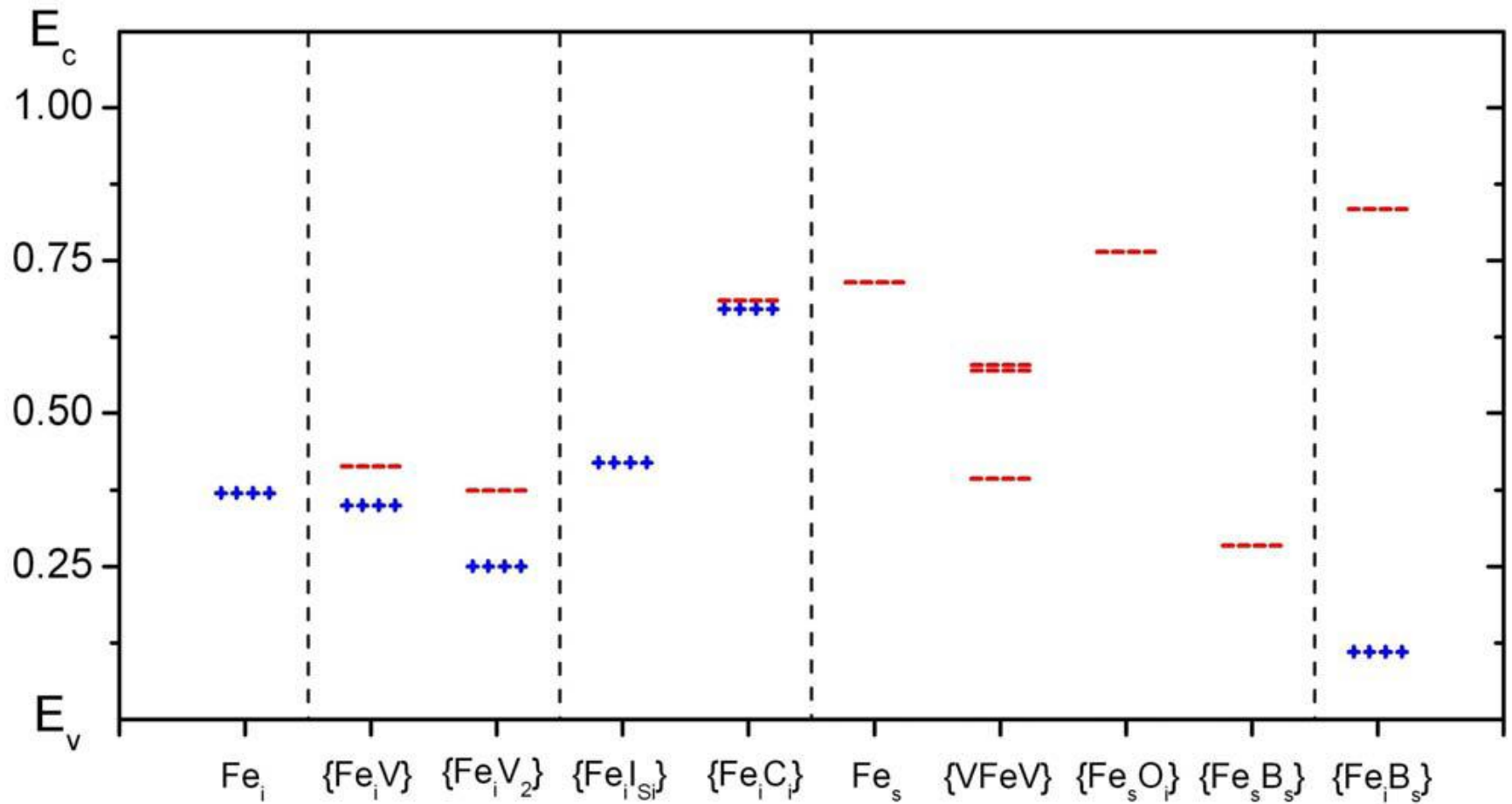
Thickness ~200  $\mu\text{m}$

Single Fe atom implantation deeply into p-n junction

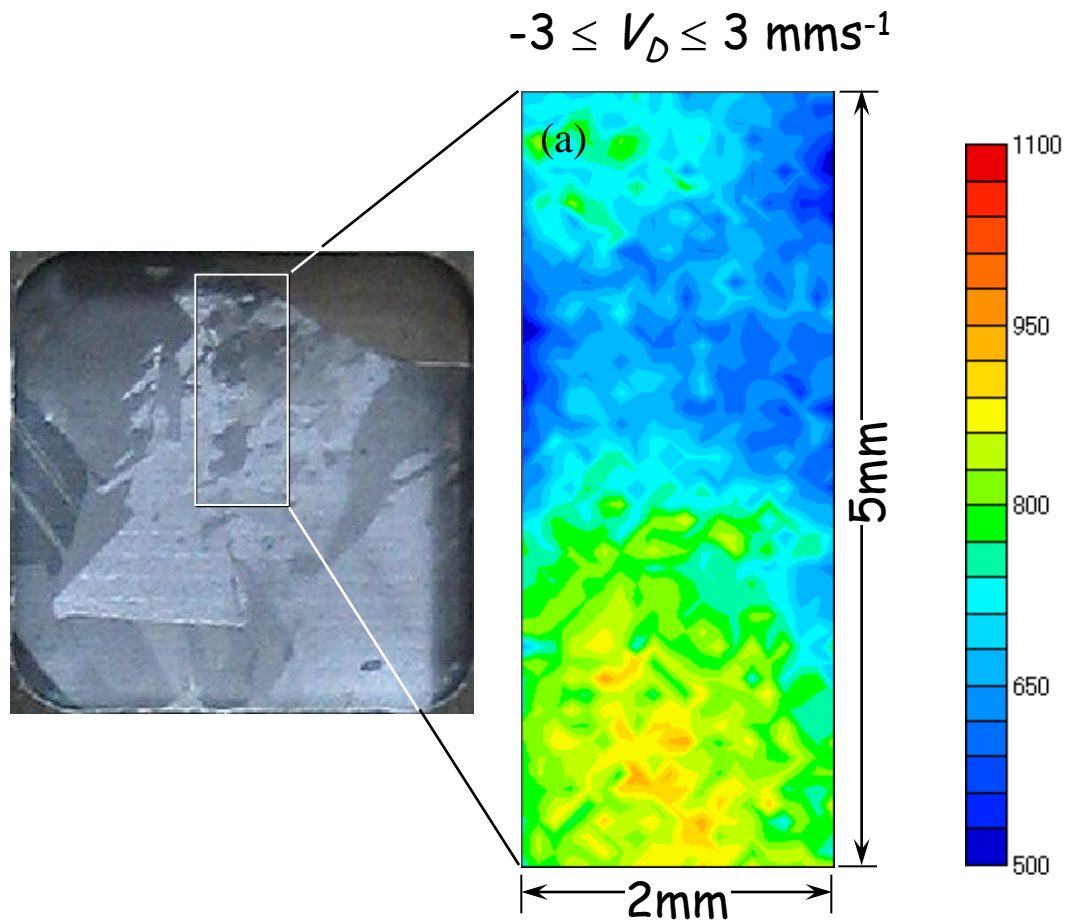


# Iron in silicon: Interactions with radiation defects, carbon, and oxygen

S. K. Estreicher,\* M. Sanati, and N. Gonzalez Szwacki  
PHYSICAL REVIEW B 77, 125214 2008



# Observed images of 1.5 nm-<sup>57</sup>Fe deposited mc-Si (intentionally contaminated with <sup>57</sup>Fe)

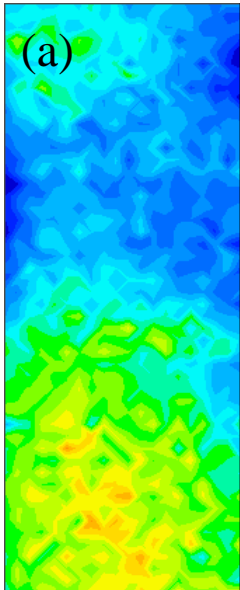


Clearly shown is that <sup>57</sup>Fe distribute differently in different crystal grains

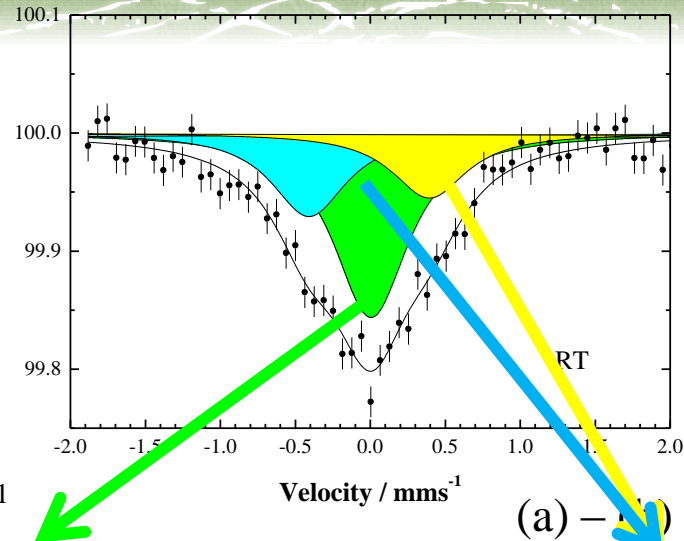
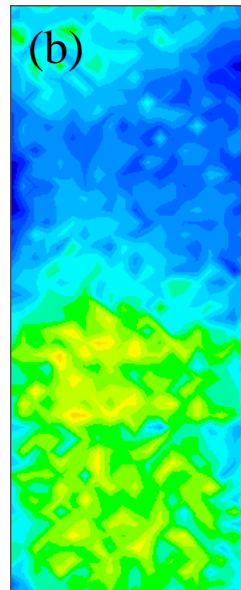
# Different resonance conditions provide different images

All  $^{57}\text{Fe}$   
components

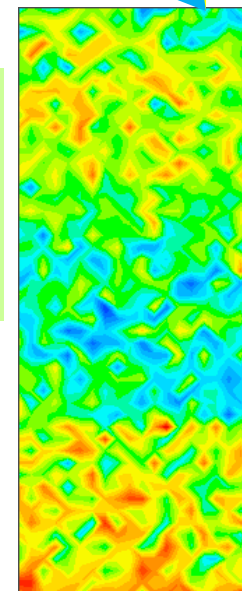
$$-3 \leq V_D \leq 3 \text{ mms}^{-1}$$



$$V_D = 0 \text{ mms}^{-1}$$

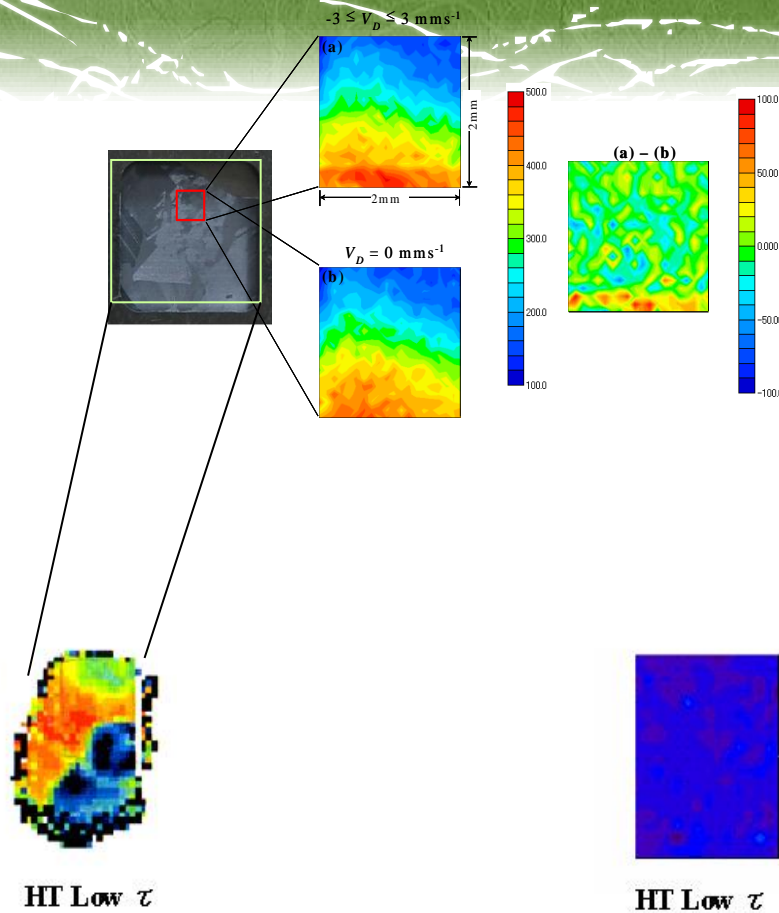


The image mainly  
corresponding to  
substitutional  
 $^{57}\text{Fe}$  component



The image mainly  
corresponding to  
interstitials and  
other clusters

# Comparison with the results from minority carrier life-time & FTIR



0  $\mu\text{s}$   2.5  $\mu\text{s}$

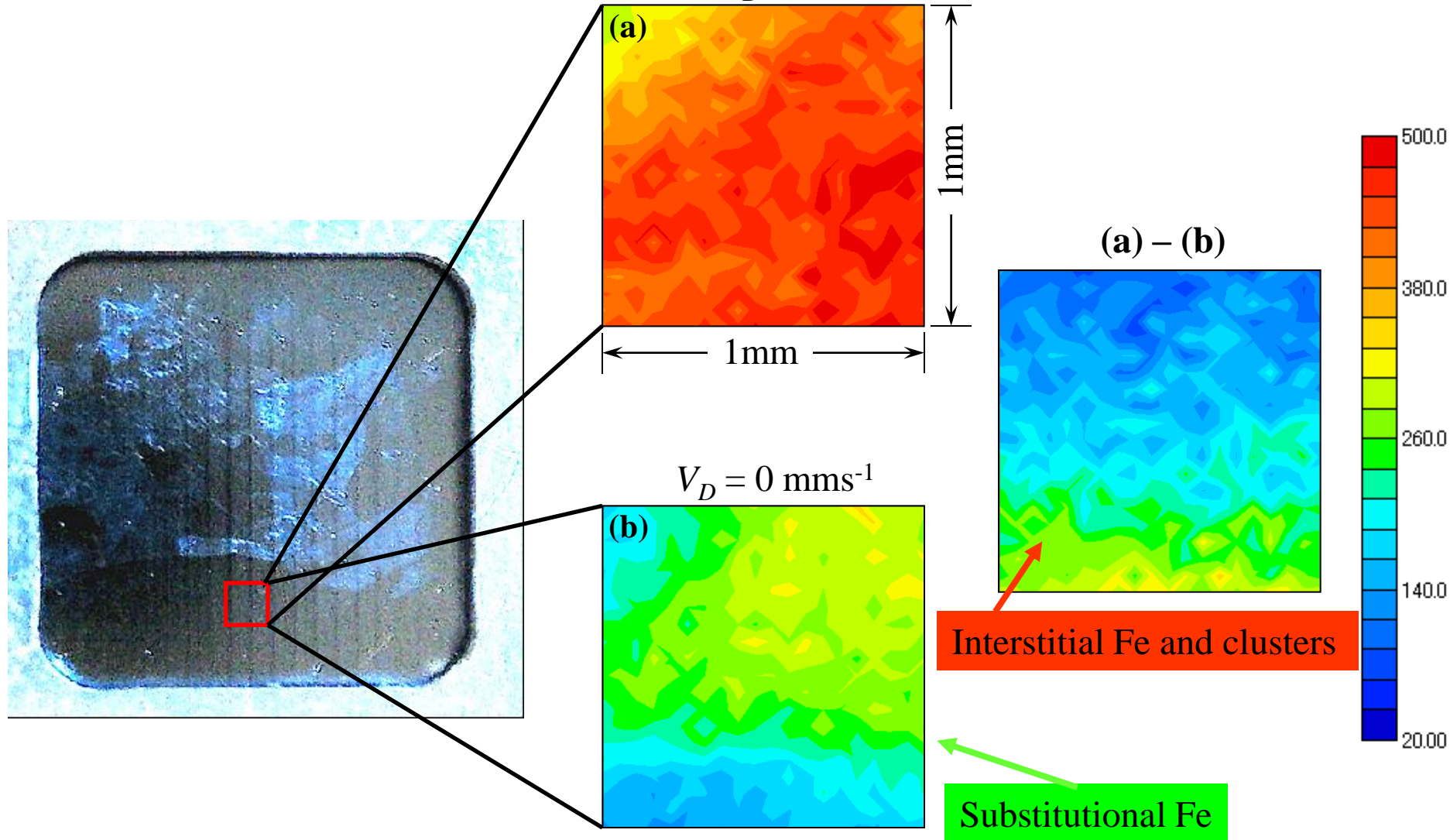
Life time

0  0.05

FTIR mapping for isolated  $O_{\text{int}}$

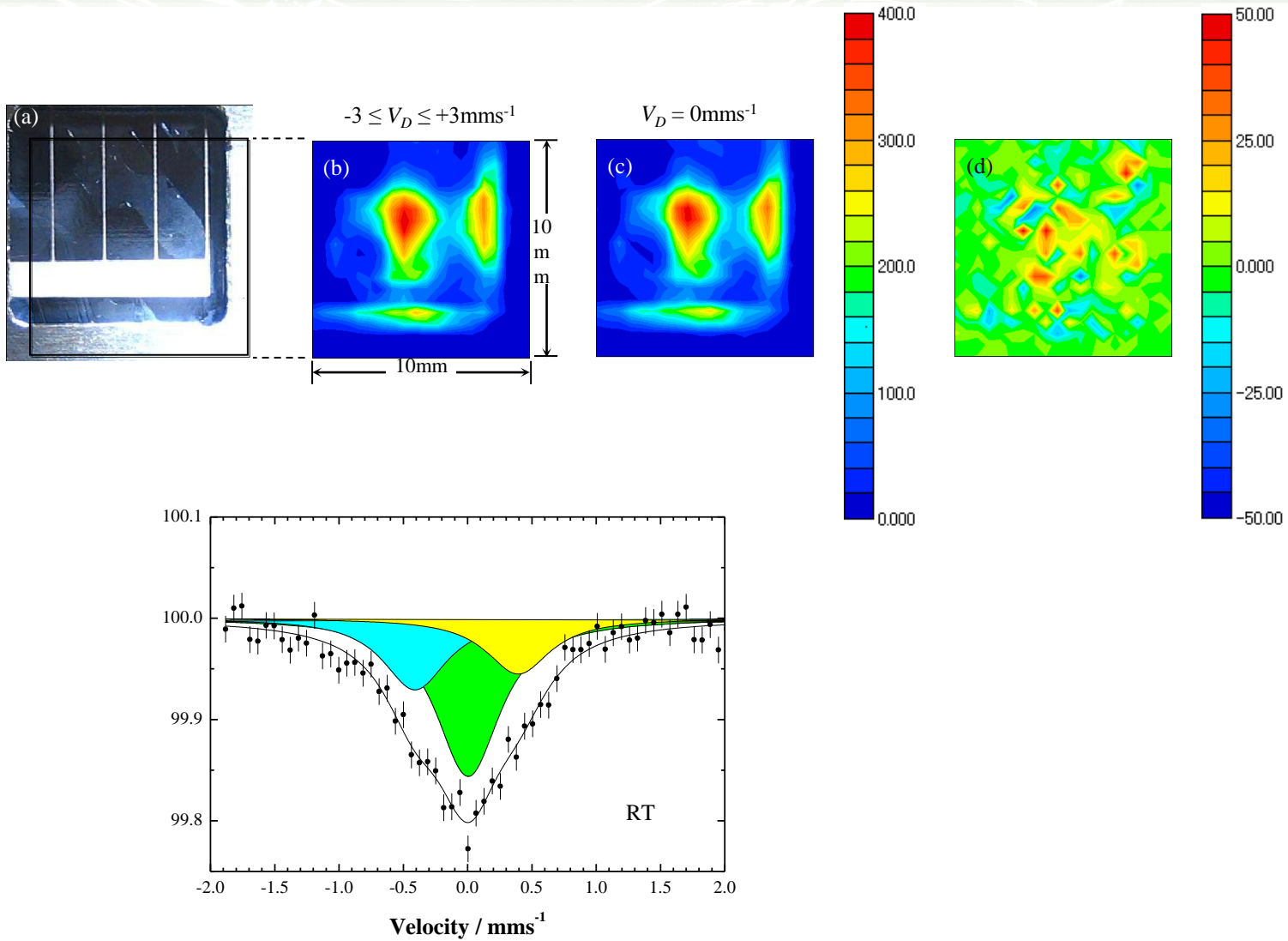
# Observed images of mc-Si as received without intentional $^{57}\text{Fe}$ contamination

$$-3 \leq V_D \leq 3 \text{ mms}^{-1}$$



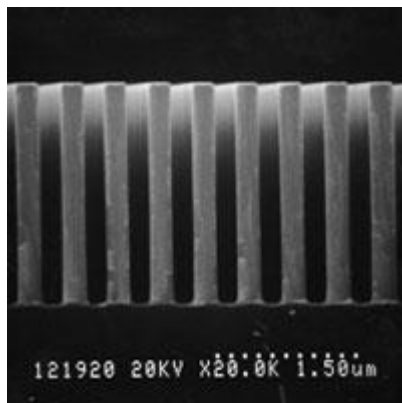
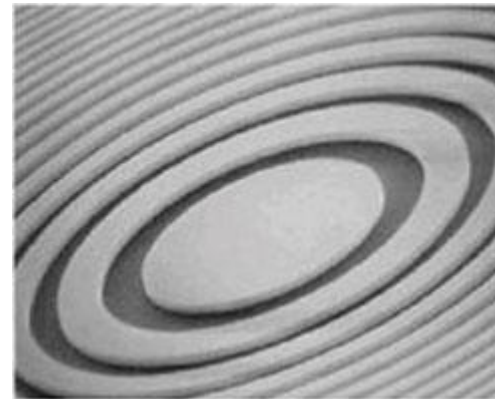
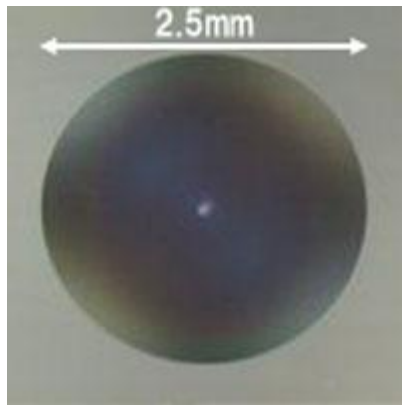


# pn-junction Si as received

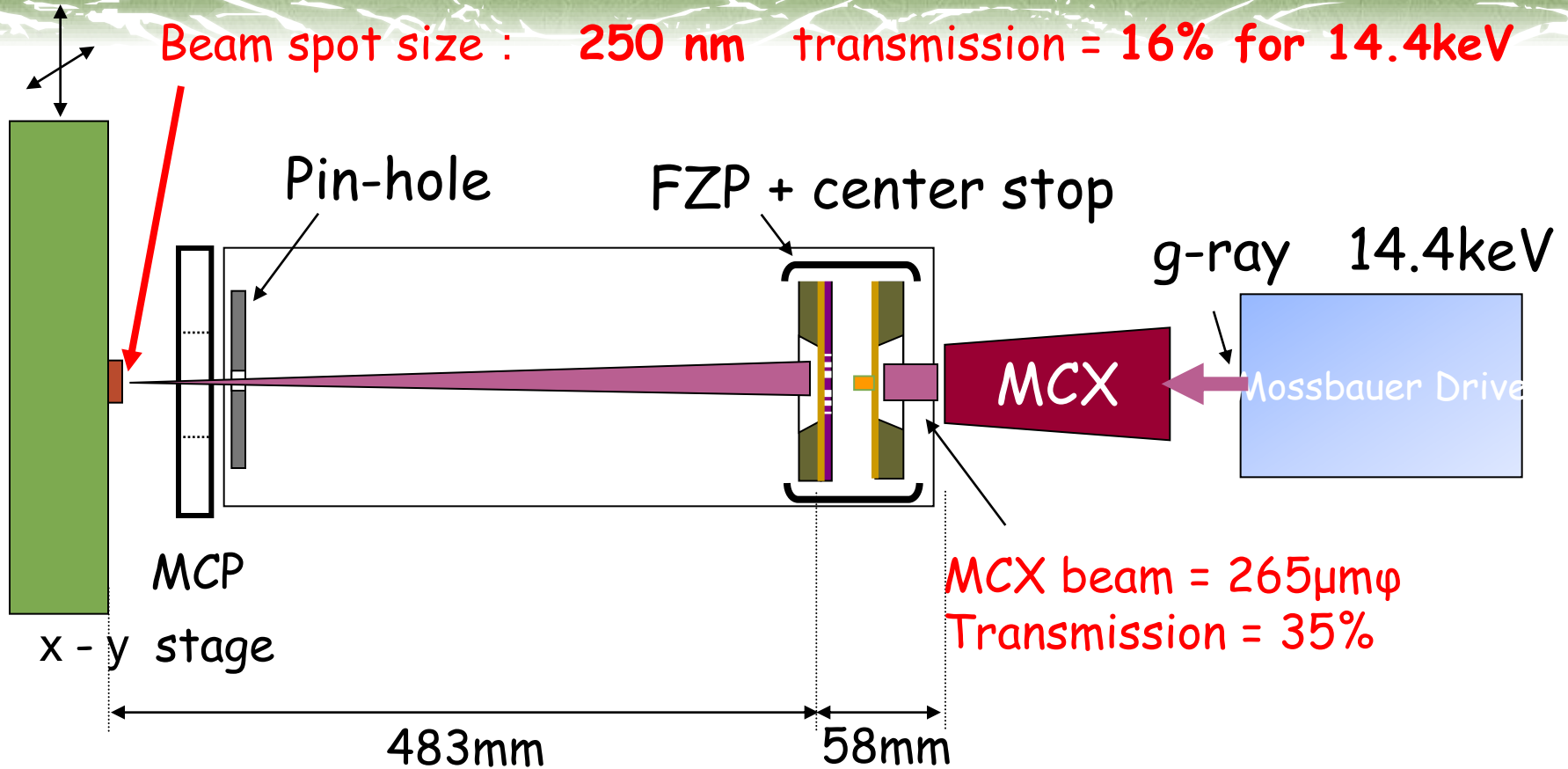


# A running project to achieve **submicron spot size**

**Fresnel Zone Plate** :  $\varphi 250\mu\text{m}$ , Ta thickness=2.5 $\mu\text{m}$ ,  
width of most outer zone= 250nm, membren : SiN 2.0 $\mu\text{m}$

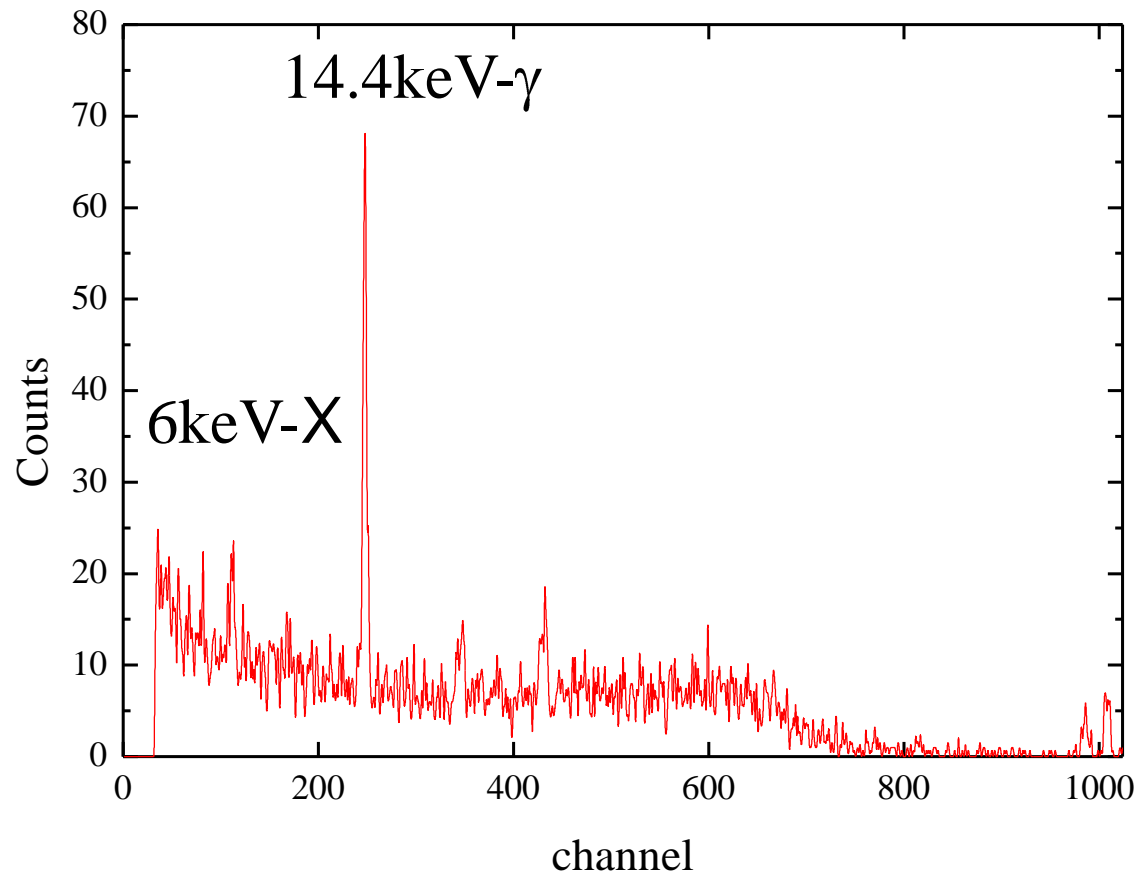


# Fresnel Zone Plate combined with MCX

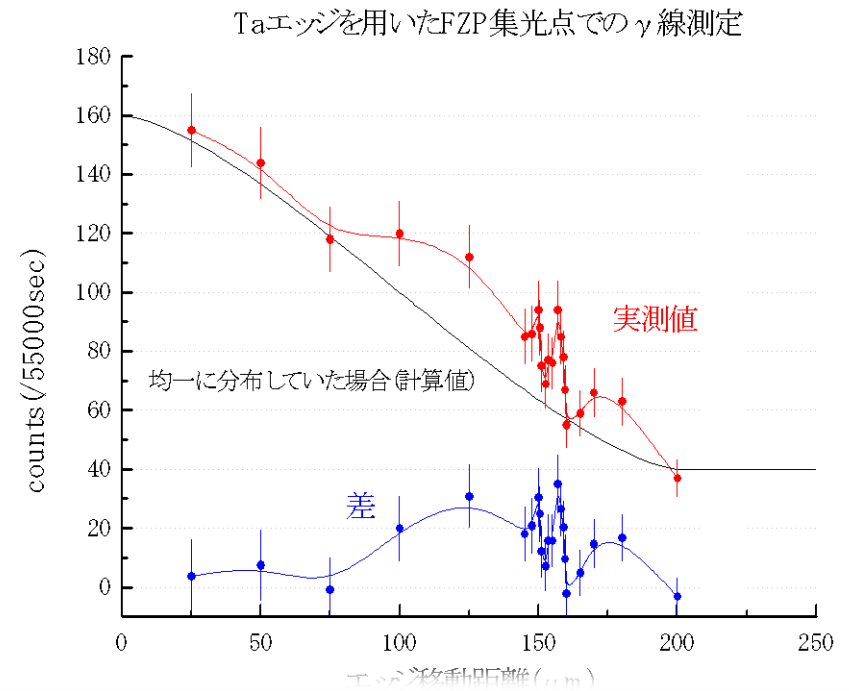
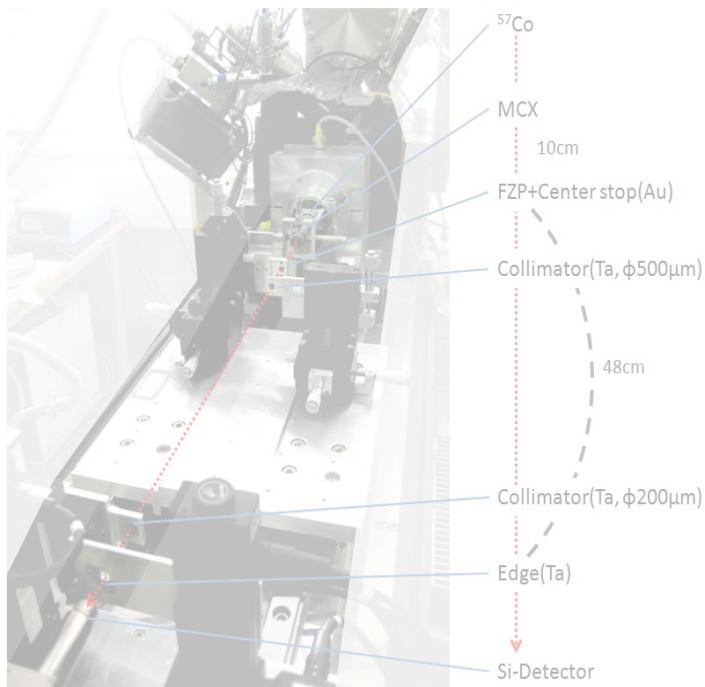


FZP ( ATN/FZP-200/206 ) focal distance = 483mm

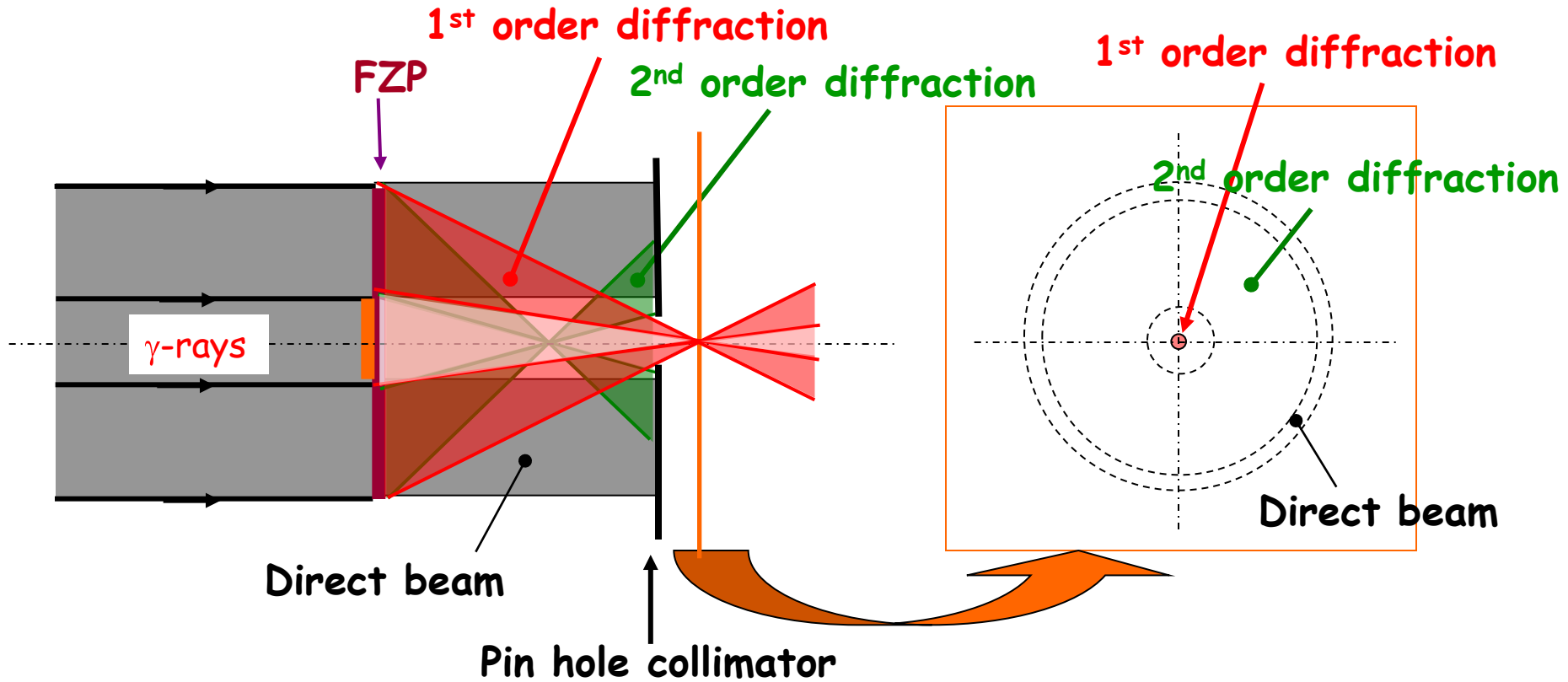
# PHA spectrum of MCX+FZP at focal point



# The spot size reaches down to 3 $\mu\text{m}$ .



# Beam focus by FZP and other elements



# Summary: "Mössbauer Camera"

1. Imaging by PIAS+FOS
  - » Monochrometer for 14.4keV  $\gamma$ -rays
2. Mapping by MCX: spatial resolution of 50  $\mu\text{m}$ 
  - » distortion of image
3. Applications for Fe impurity in Si-solar cells
  - » mapping under light illumination
4. Mapping by MCX + FZP: spatial resolution of 3  $\mu\text{m}$ 
  - » vibration of the set-up

# ICAME2011 in Tokyo

supported by YAMADA Science foundation  
to create the next generation of ICAME

25-30 September 2011

Center for National University  
Finance and Management,  
Tokyo, JAPAN



and Screens - (Og  
「富神風神図」

